

Silicon Integrated Nanophotonics: Road from Scientific Explorations to Practical Applications



Dr. Yurii A. Vlasov,
Manager, Silicon Integrated Nanophotonics

1989

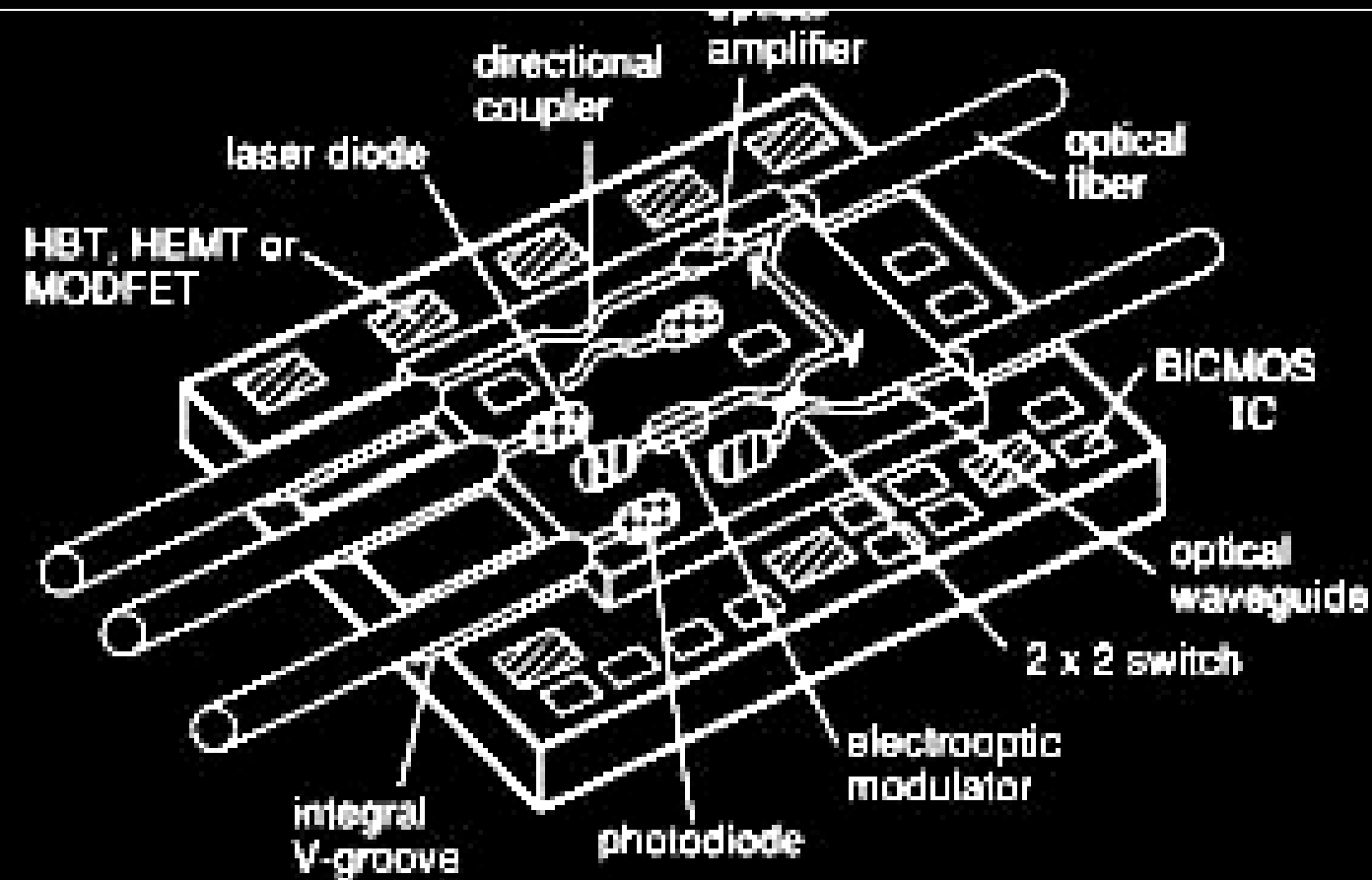


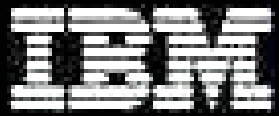
Fig. 3. Silicon-based OEIC "superchip," similar to the one proposed by Abstreiter [2].

Concept:

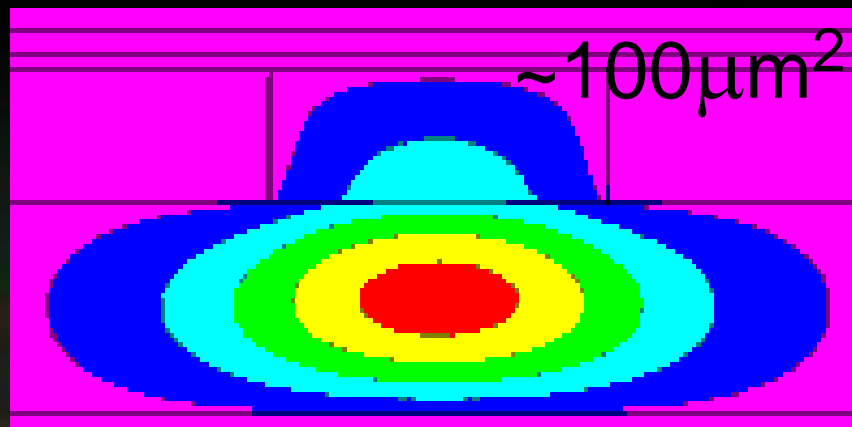
1. Deep scaling of optics
2. CMOS compatible
 - Materials
 - Processing

R. Soref et al

Si Photonics scaling in 2 decades: 1985 - 2005

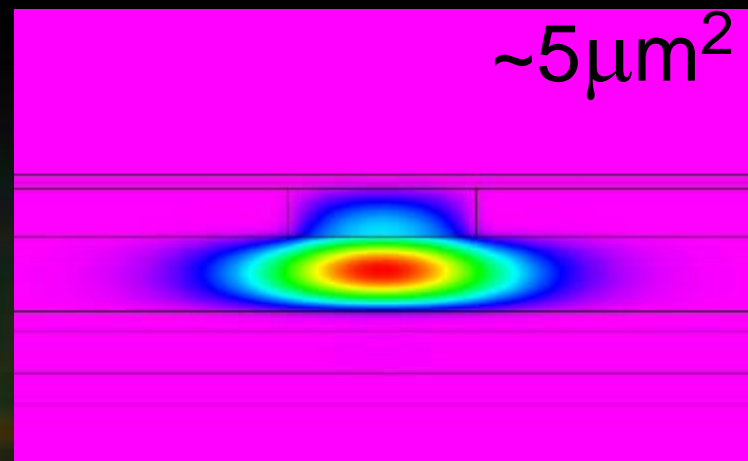
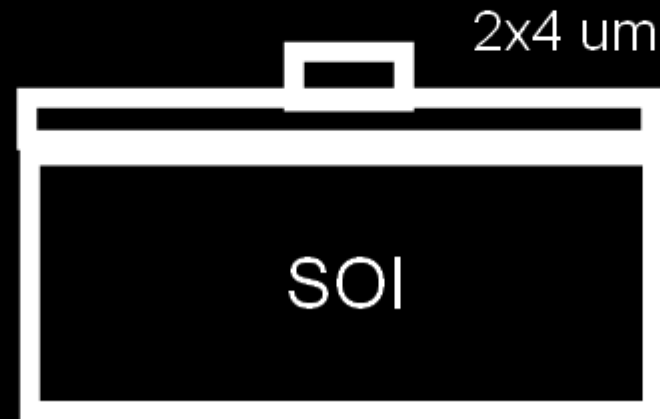


Diffused wg
Doped Si



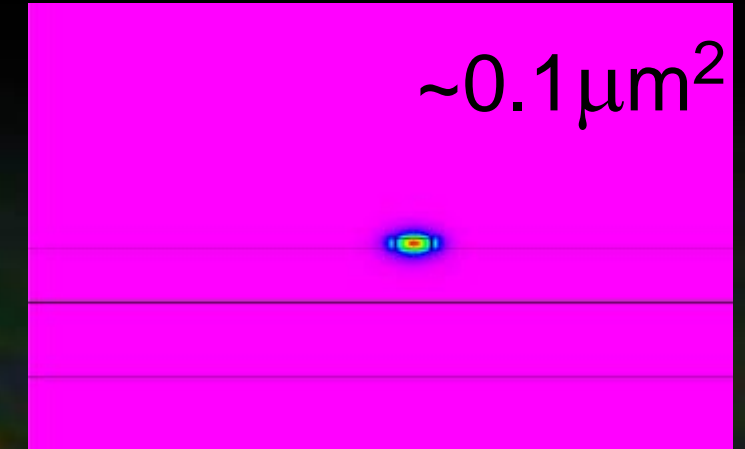
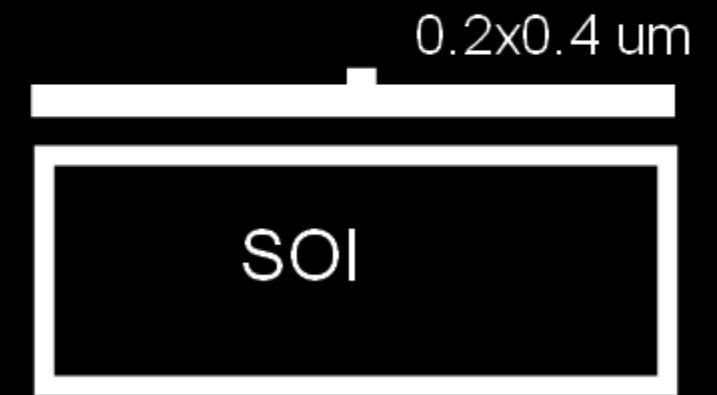
$R \sim 10\text{cm}$

Rib wg
SIMOX



$R \sim 1\text{cm}$

Strip wg
Unibond



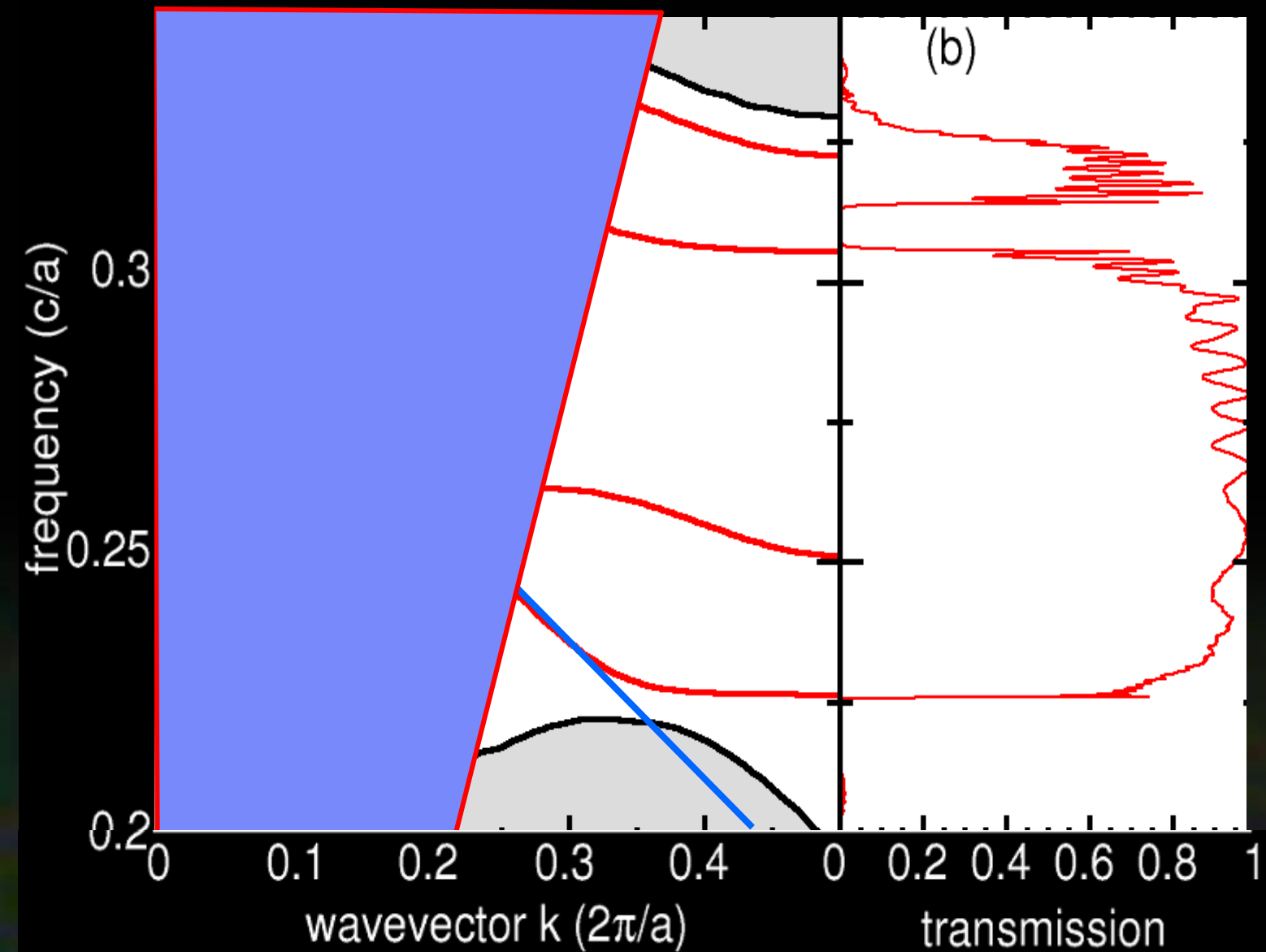
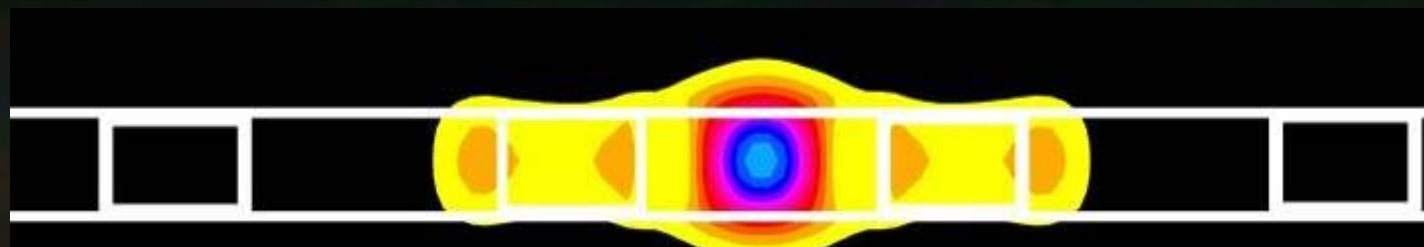
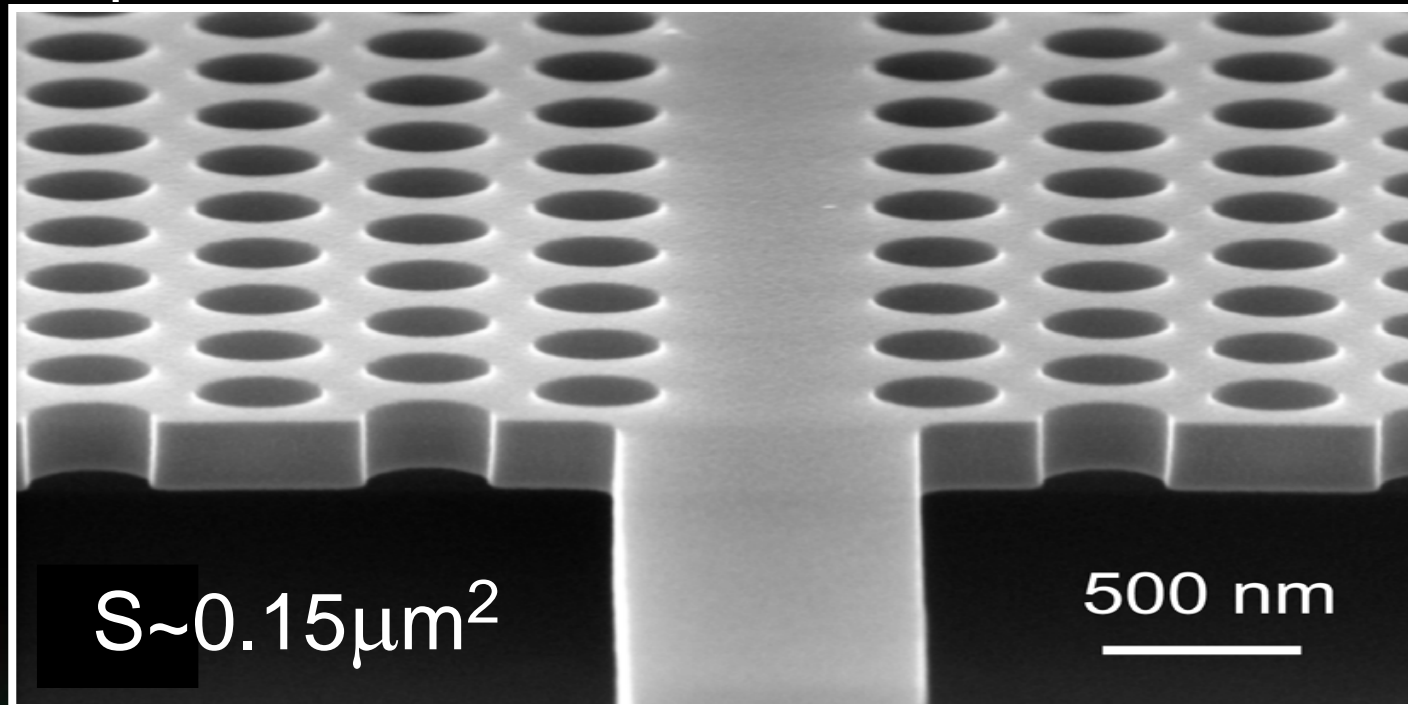
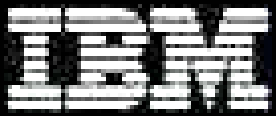
$R \sim 1\mu\text{m}$

Higher refractive index contrast=smaller bending radius=higher integration density

Planar SOI photonic crystals

holes 300nm

pitch 450nm

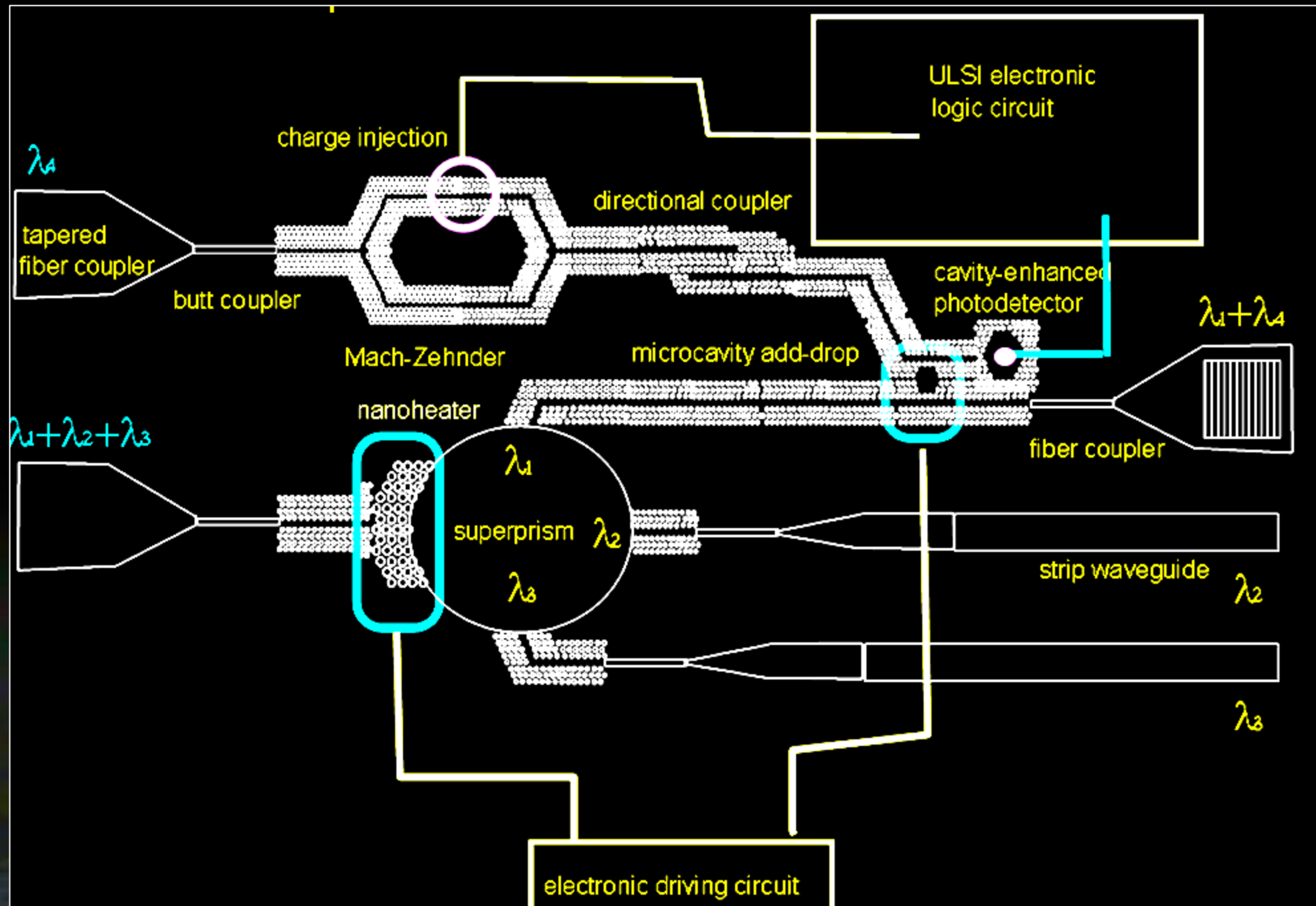
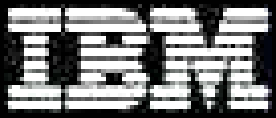


Very slow group velocities

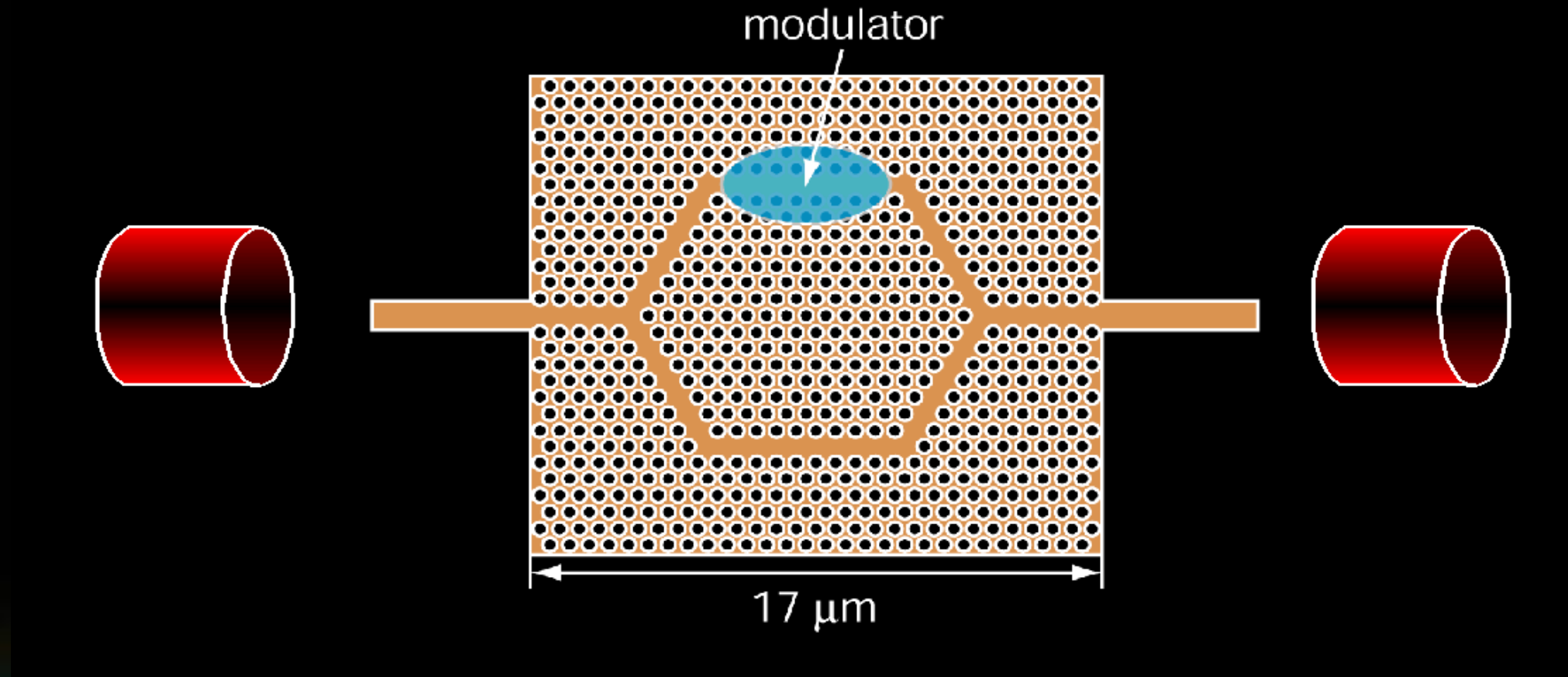
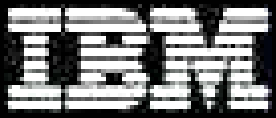
Mode is strongly confined to the center of wg

S.McNab et al, OE, April 2003

Nanophotonics Toolbox (circa 2002)

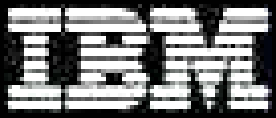


Design of PhC based MZI

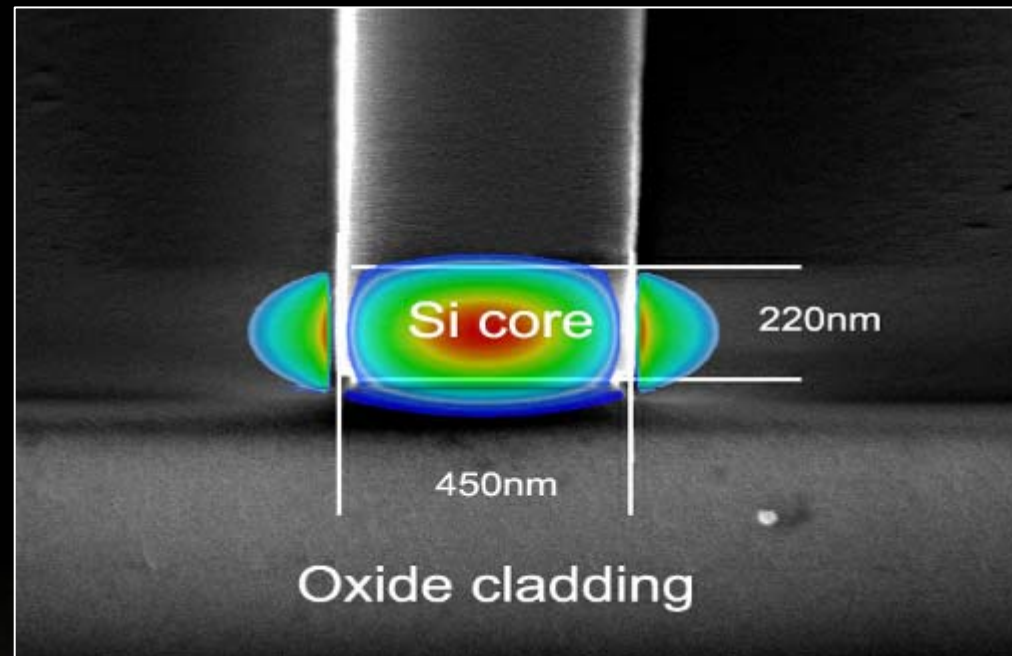


- | | |
|-------------------------|---|
| •fiber-to-strip coupler | 2 |
| •access strip waveguide | 2 |
| •strip-to-PhC couplers | 2 |
| •splitter/combiner | 2 |
| •sharp bend | 4 |
| •phase shifter | 1 |

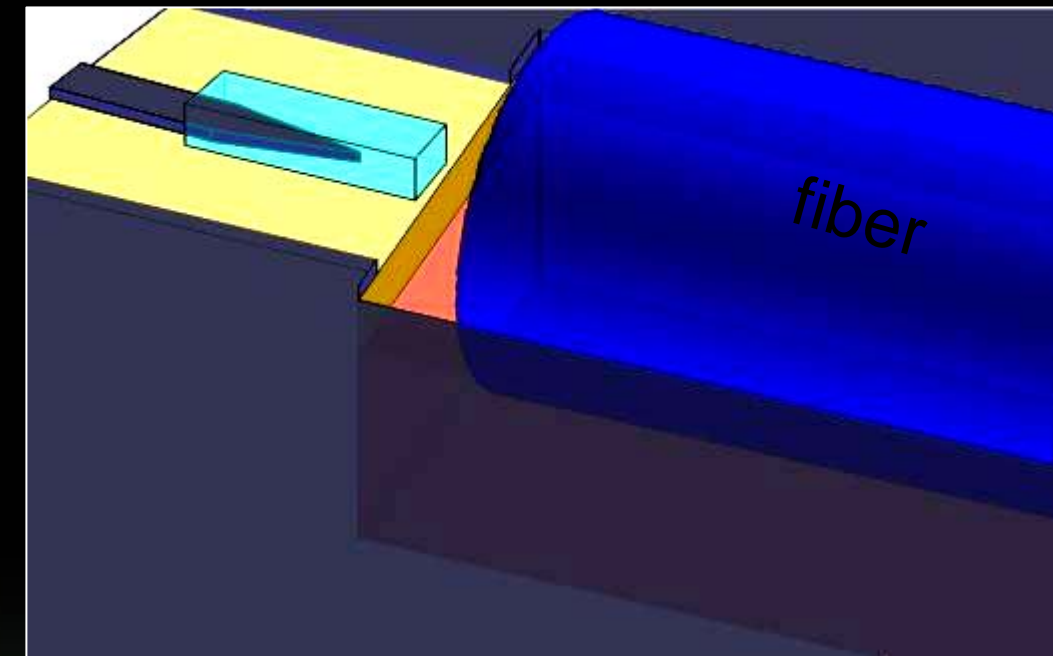
Single-mode SOI photonic wires



SOI photonic wire



Inverted Taper fiber coupler



Propagation loss

1.7 ± 0.1 dB/cm

Coupling loss

< 0.5 dB/port

Alignment tolerance at 3dB

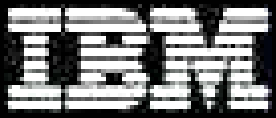
$\pm 1 \mu\text{m}$

Coupling bandwidth

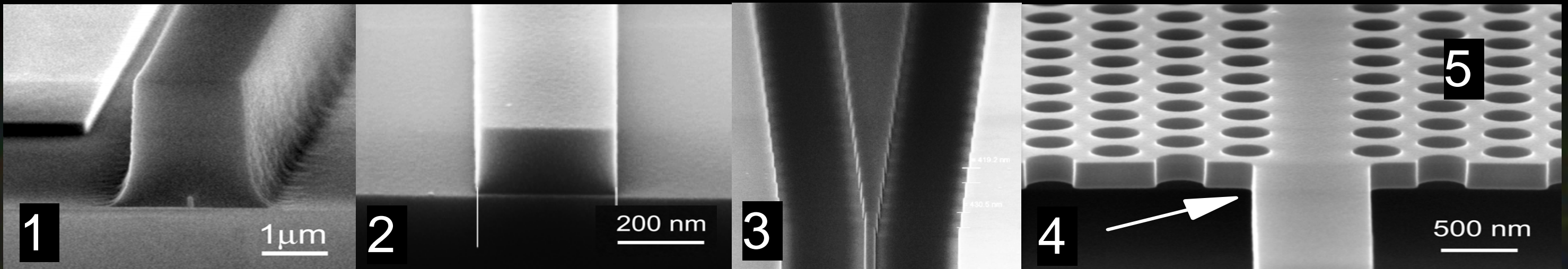
300nm

McNab, Moll, Vlasov, Opt. Exp. 11 (2003)

2003 IBM Milestone

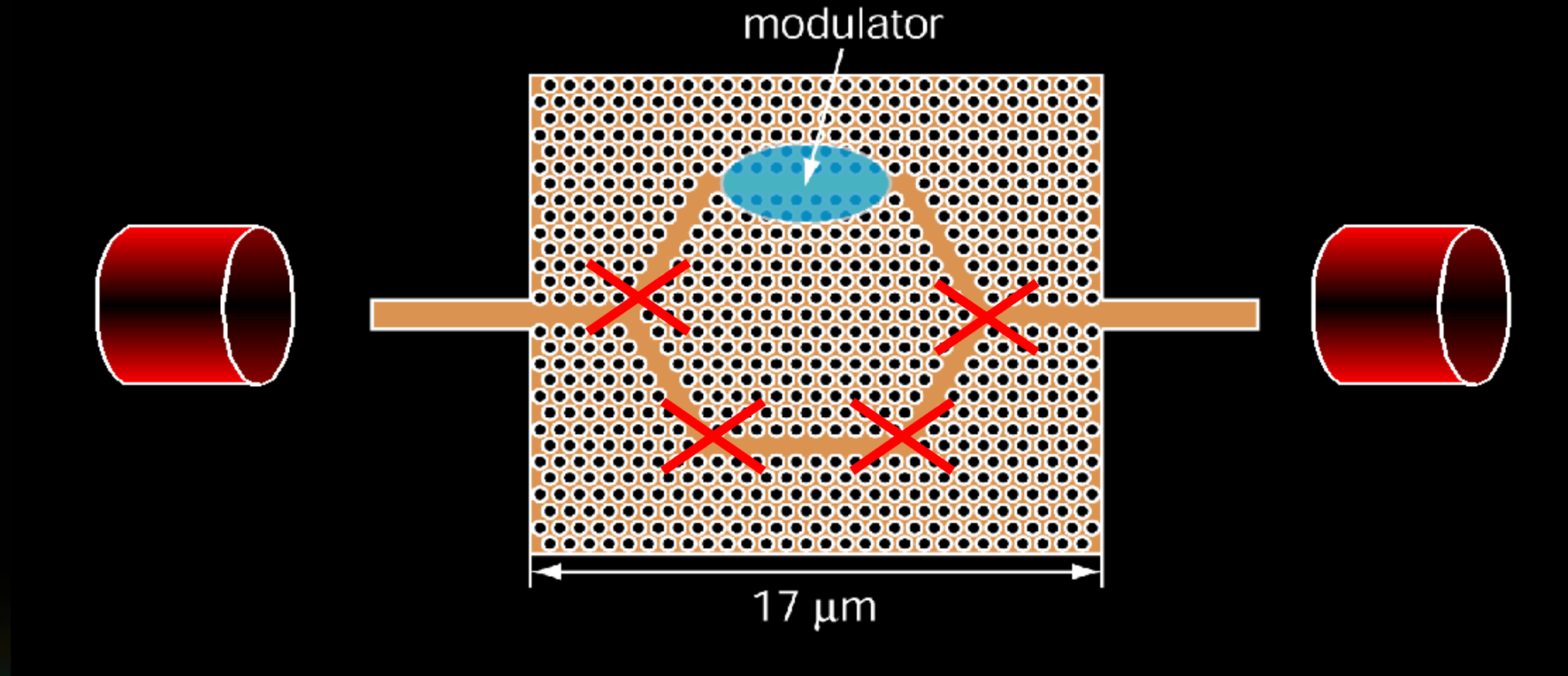
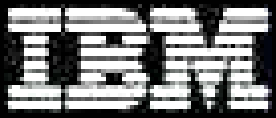


Demonstration of a complete circuit employing photonic crystal waveguides with record low losses 8 ± 2 dB/cm



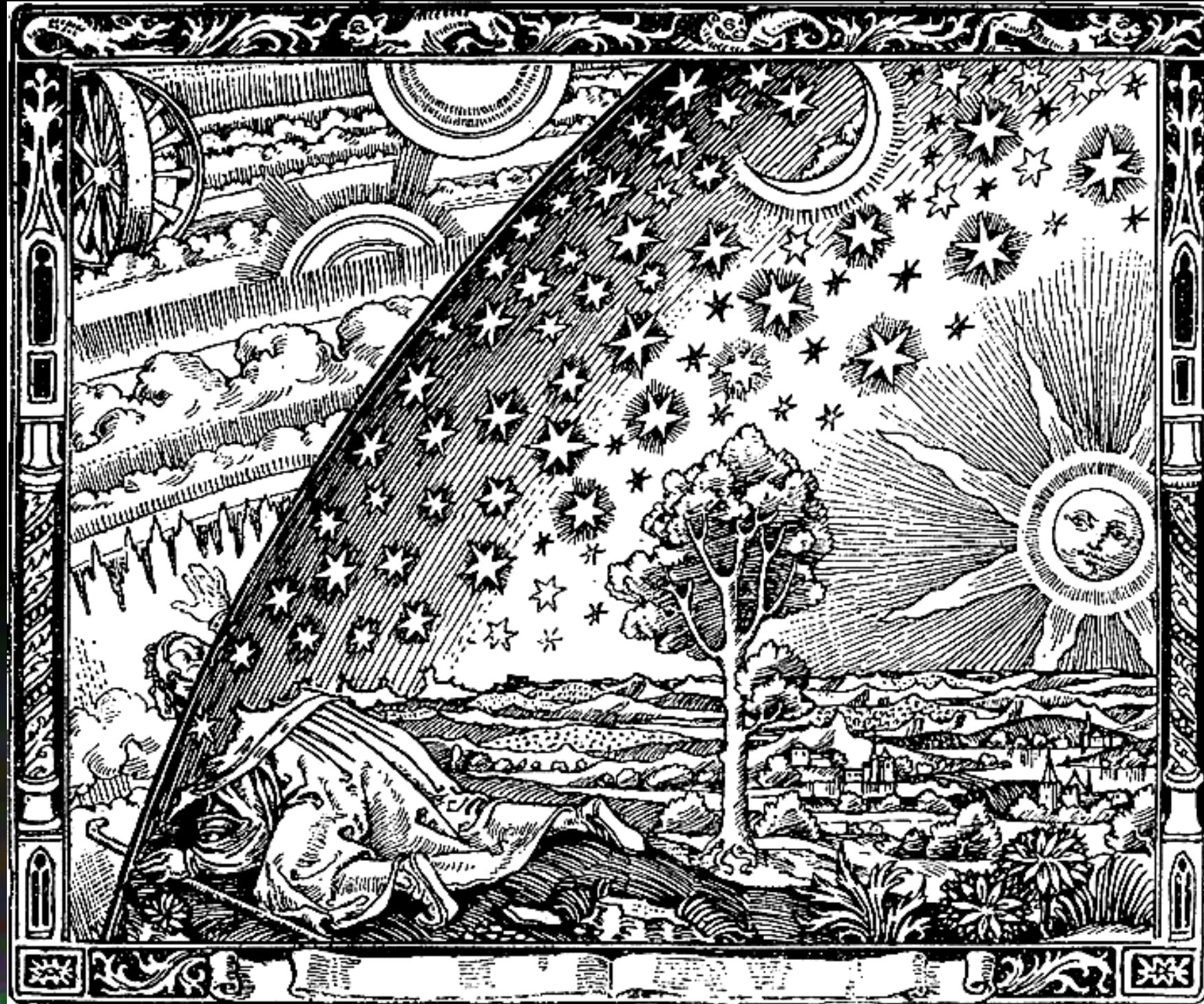
McNab, Moll, Vlasov, Opt. Exp. 11 (2003)

Design of PhC based MZI



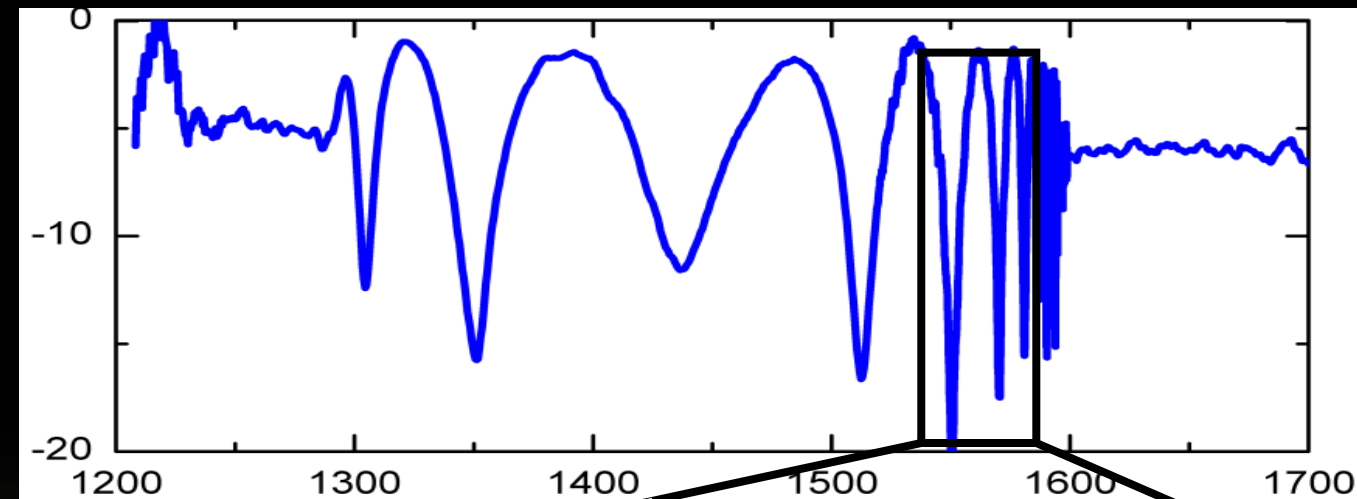
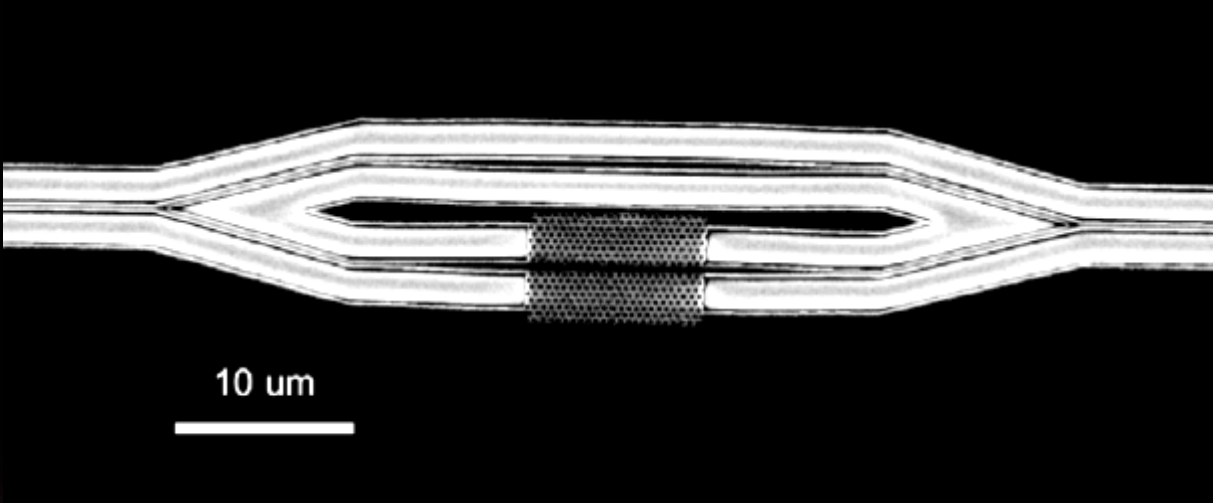
•fiber-to-strip coupler	2
•access strip waveguide	2
•strip-to-PhC couplers	2
•splitter/combiner	2
•sharp bend	4
•phase shifter	1

Breaking out of the sphere

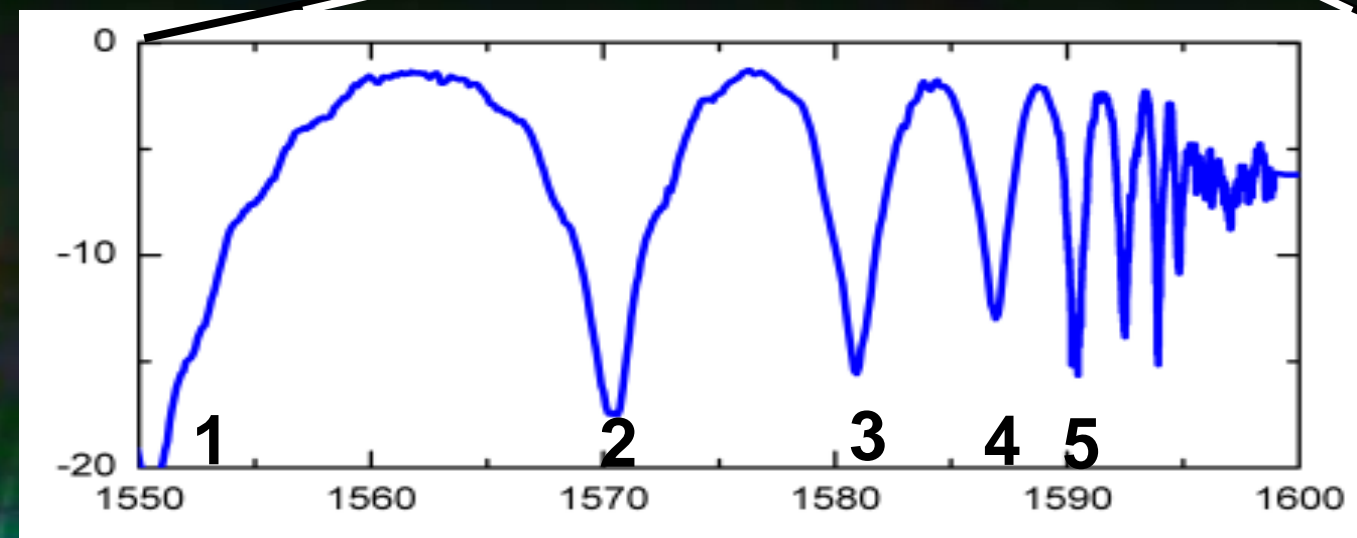


Demonstration of the passive Mach-Zehnder interferometer employing photonic crystal waveguides with losses below 3dB.

Up to 300π phase shifts



PhC Mach-Zehnder Interferometer

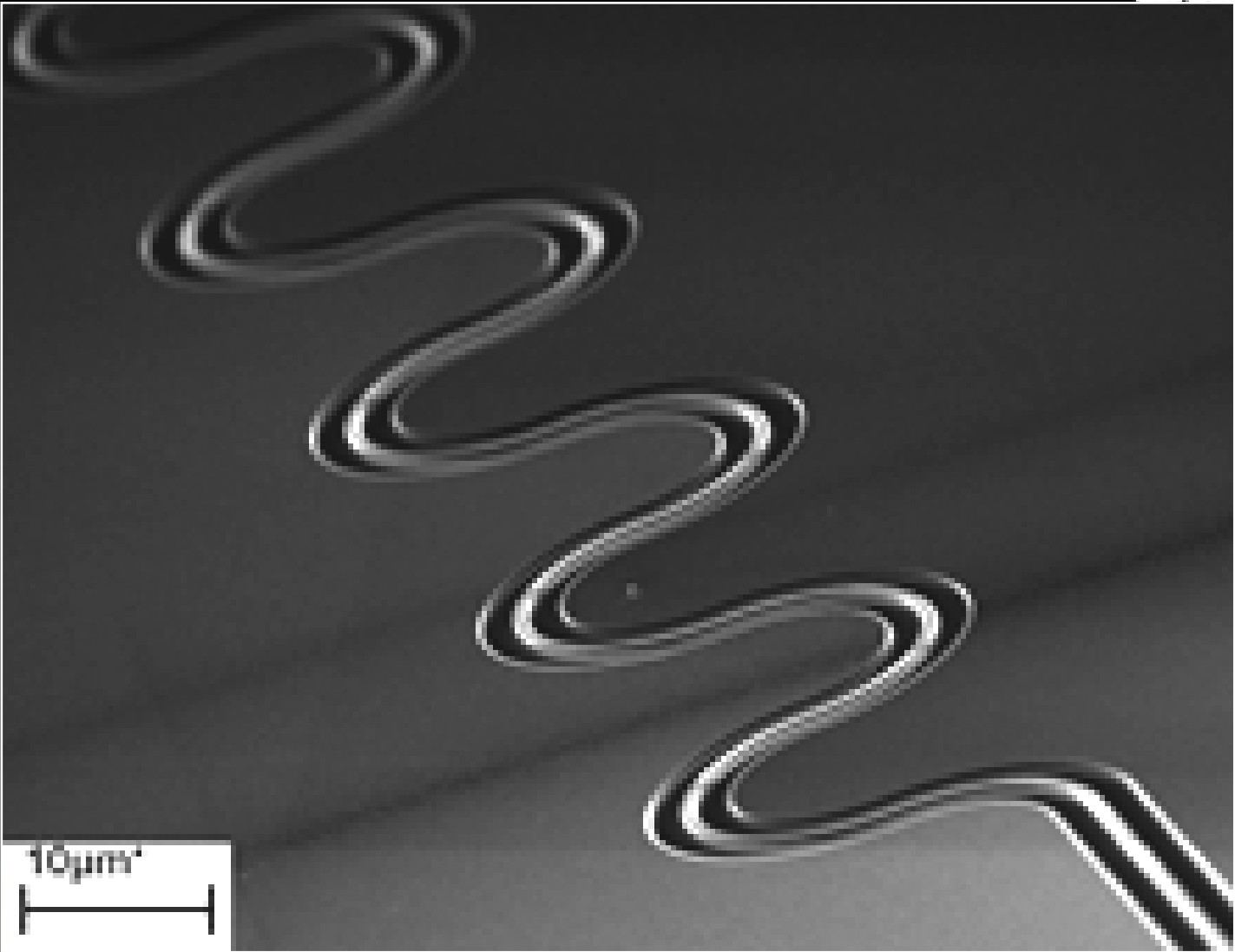


Losses in sharp bends



(measured with 20 bends)

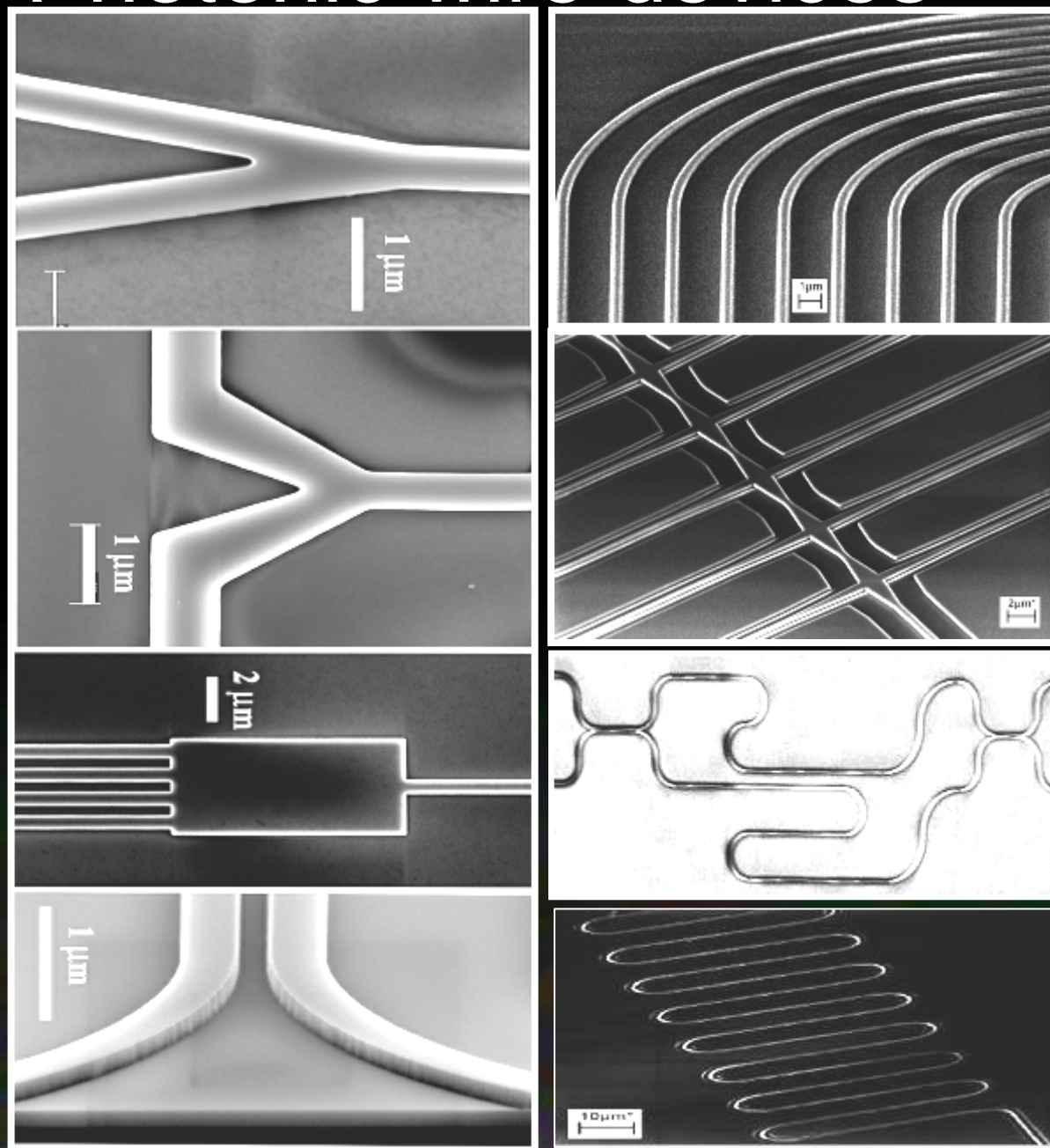
<i>R</i>	Losses per 90° bend
1um	0.086±0.005dB
2um	0.013±0.005dB
5um	0.005±0.005dB



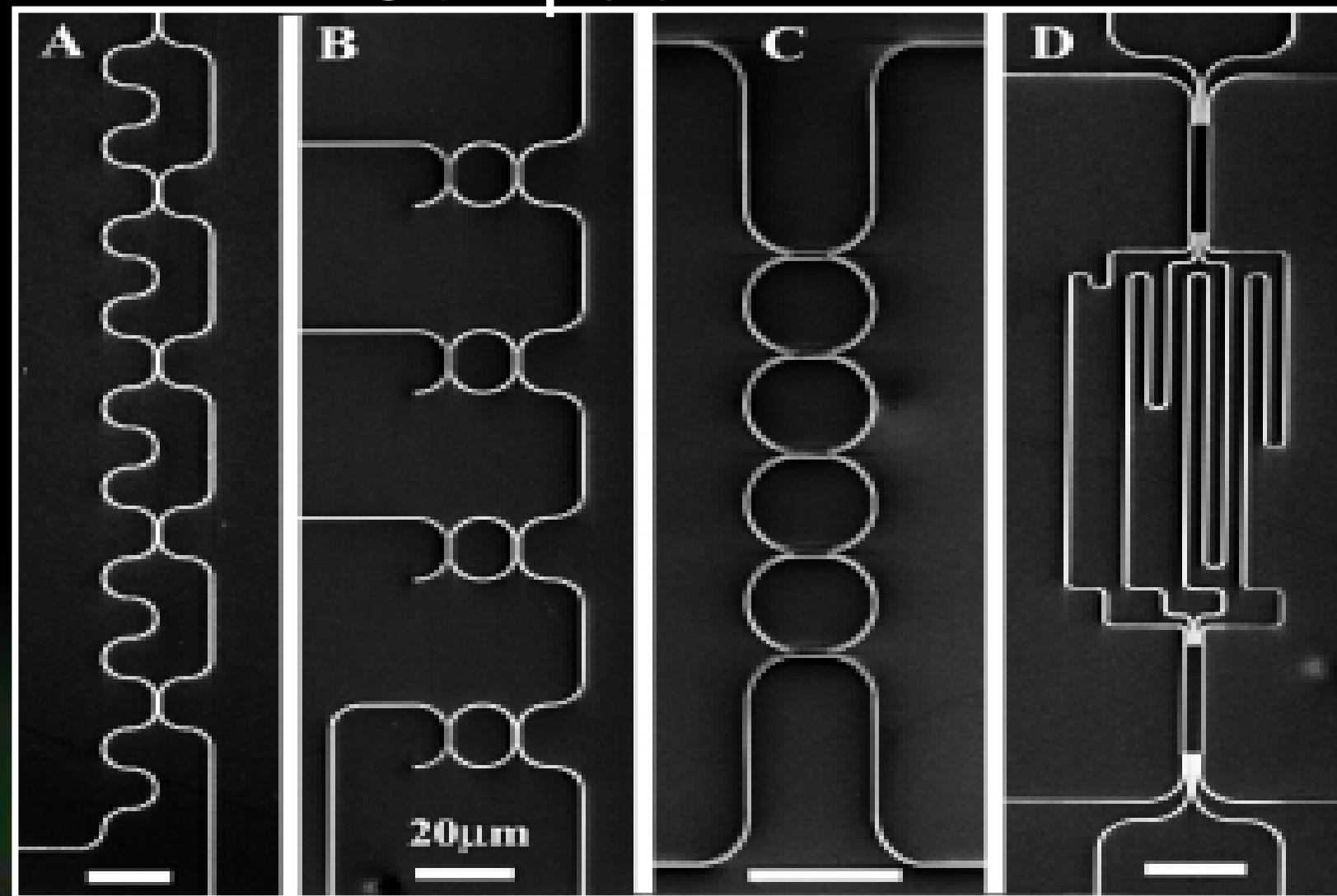
Vlasov, McNab, Opt. Exp. 12 (2004)

R=6.5um (measured with 280 bends)
Loss/90° bend 0.0043±0.0005dB
Bandwidth 250nm

Photonic wire devices

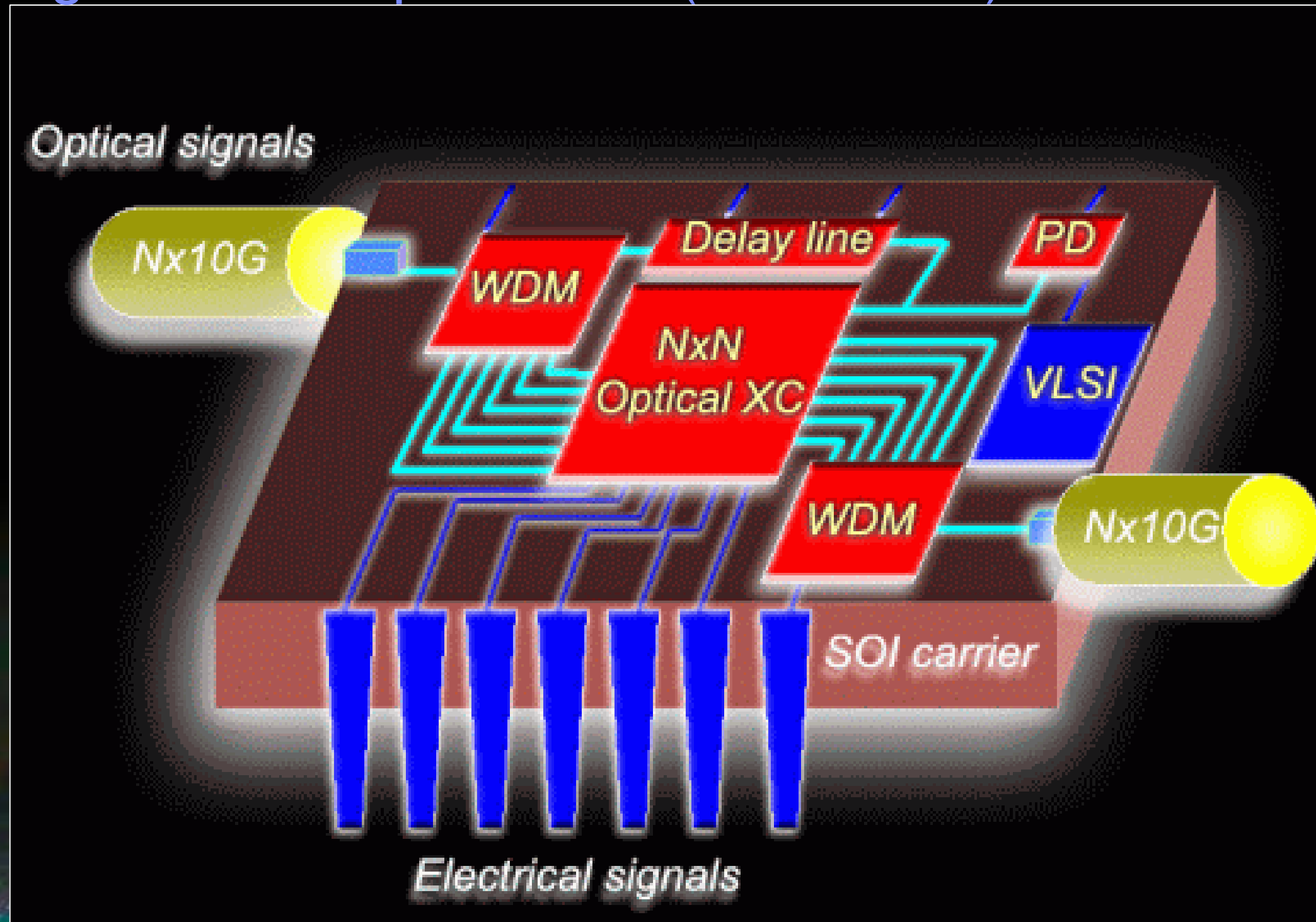
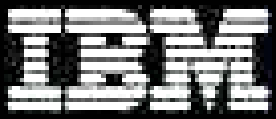


Compact WDM



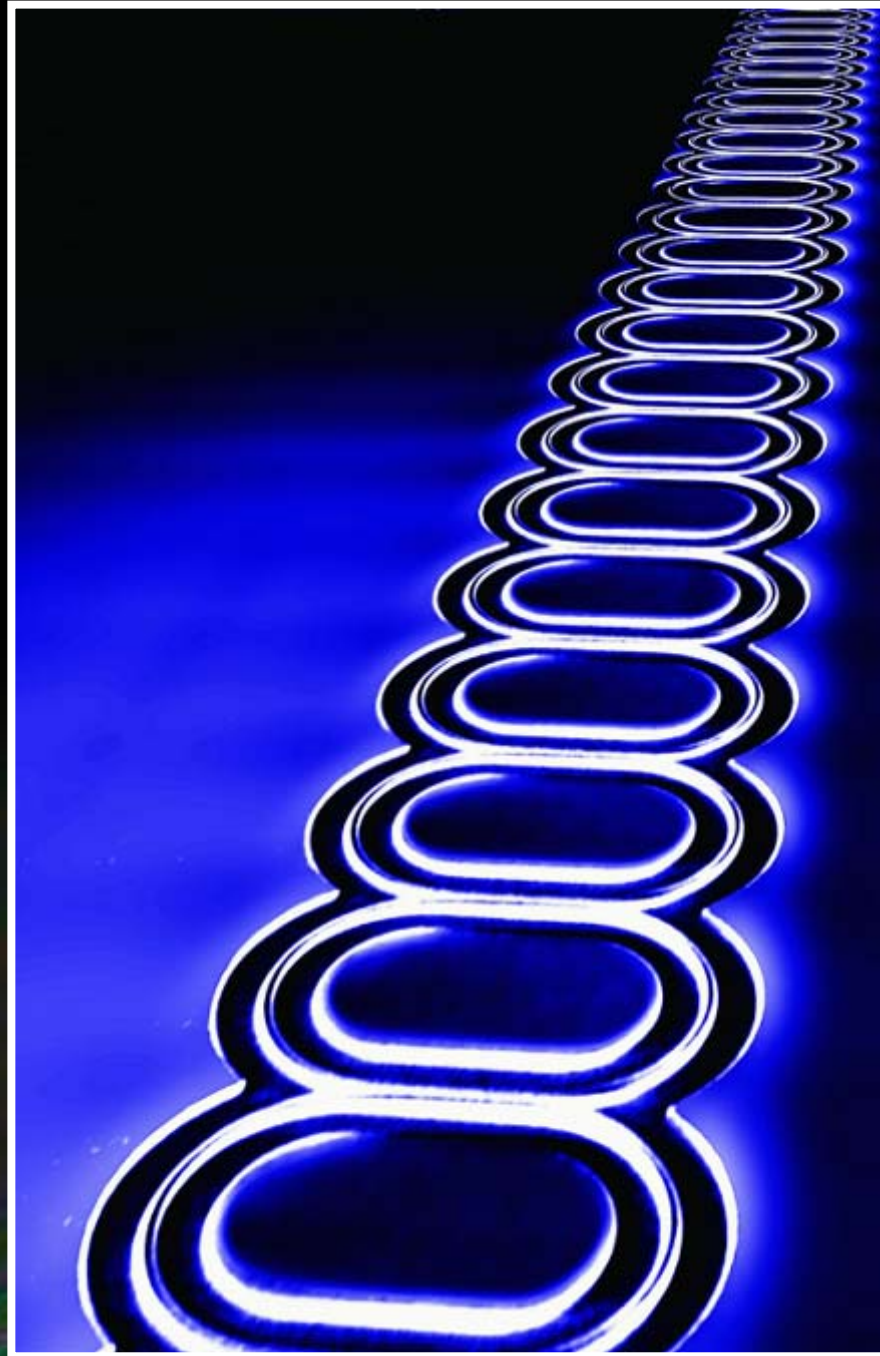
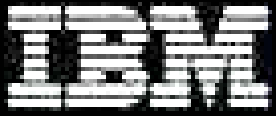
Footprint is as small as 0.03mm^2

Silicon Integrated Nanophotonics (circa 2004)



2006 IBM Milestone

Ring resonator delay line

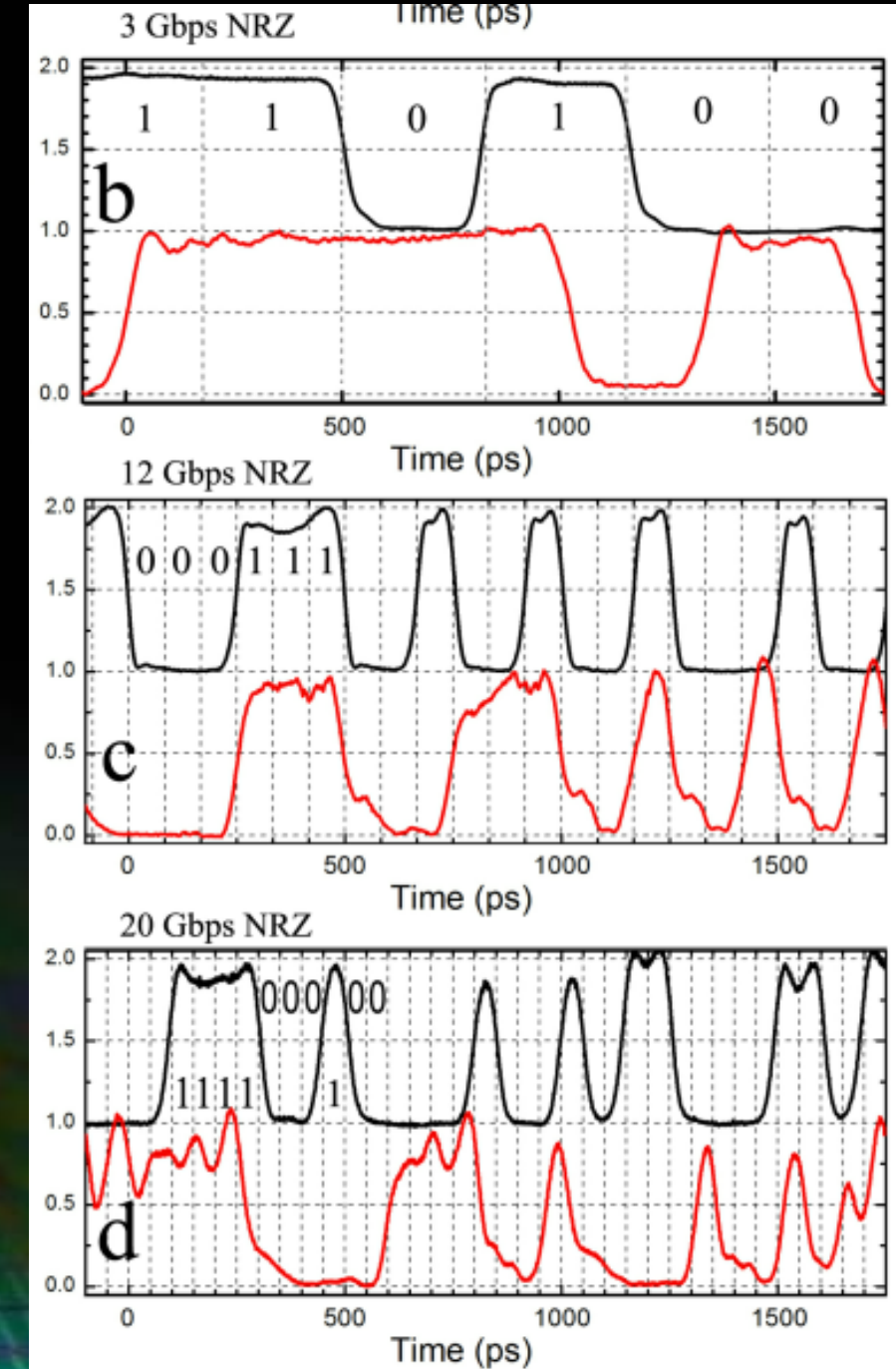


3 Gbps
12 Gbps
20 Gbps

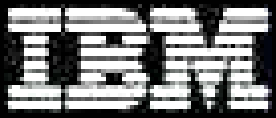
1.7 bit delay
6 bit delay
10 bit delay

- Bandwidth is inversely proportional to delay
- Loss is proportional to delay

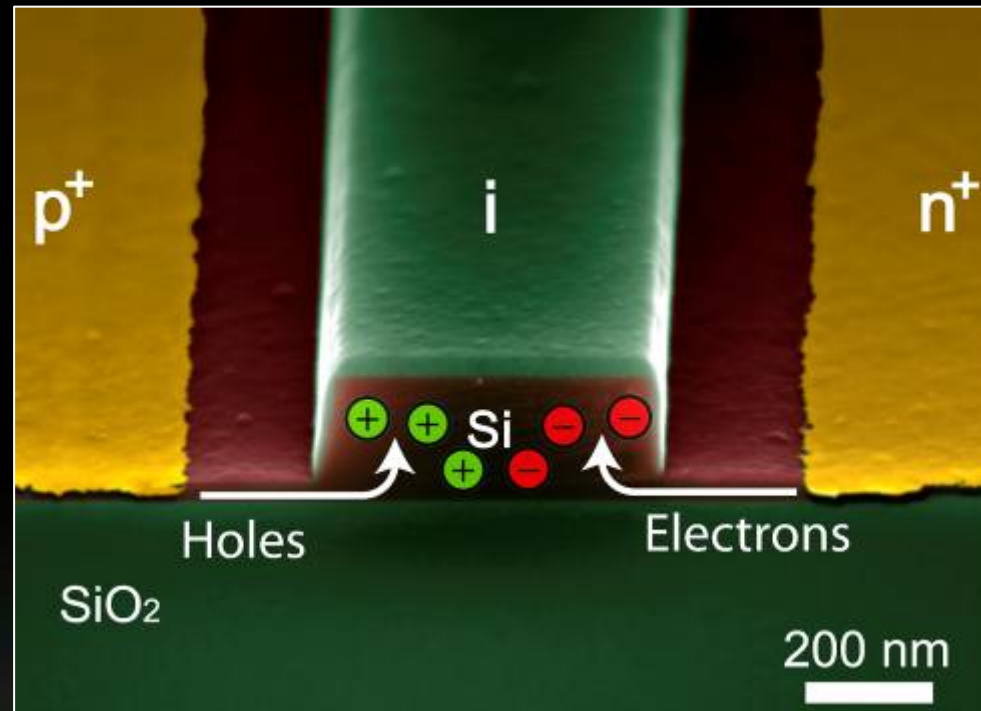
Footprint \leftrightarrow Loss
 \leftrightarrow BW \leftrightarrow Delay



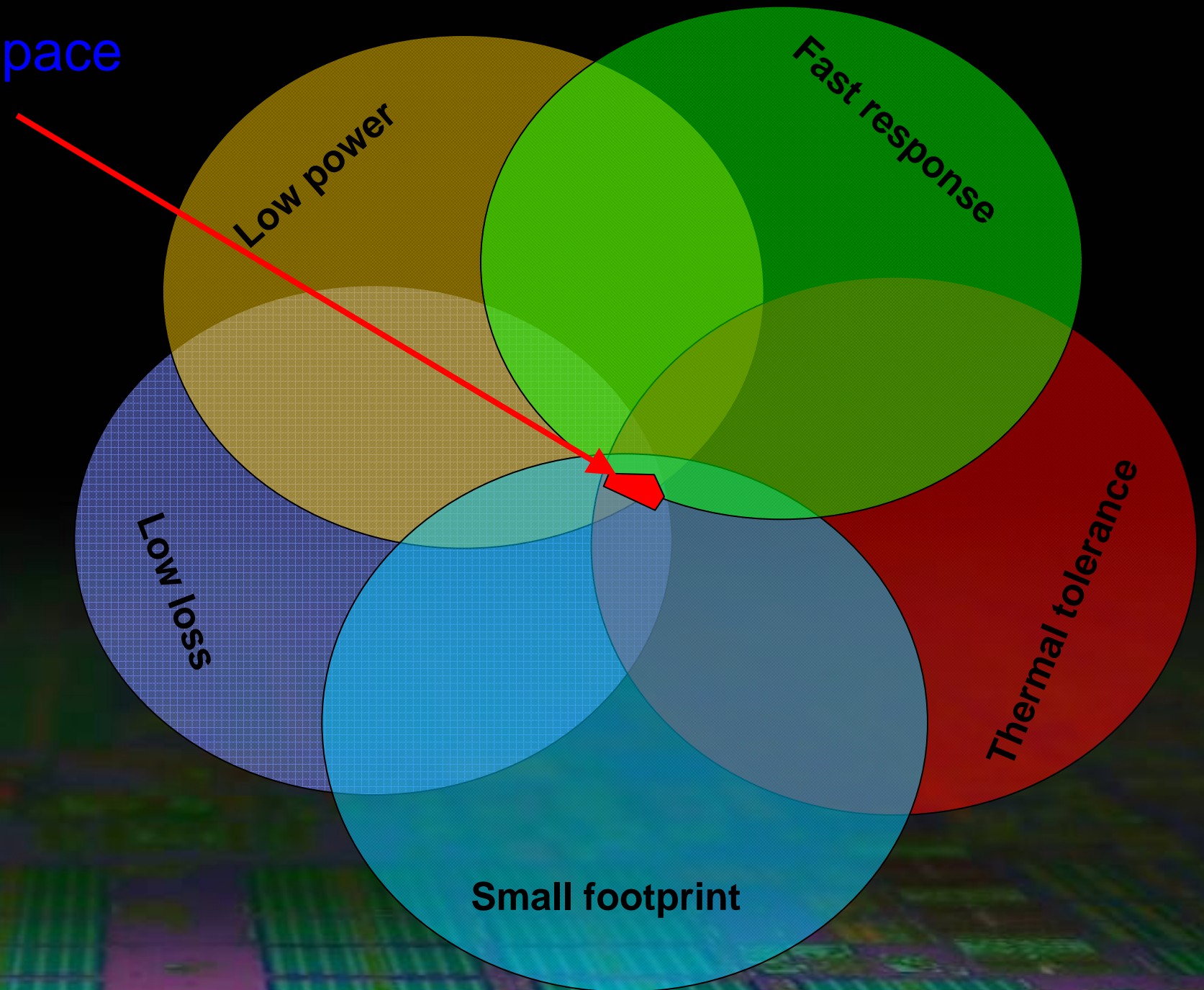
Electrooptic Device Design Space



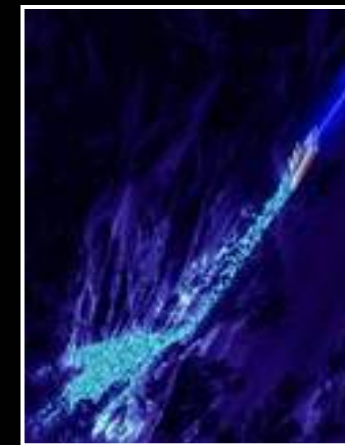
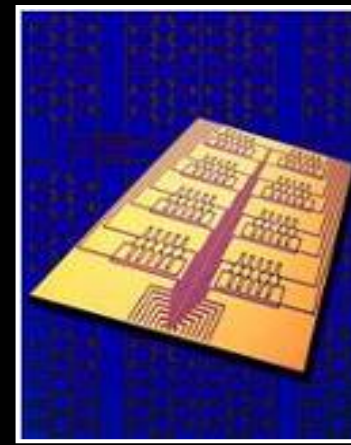
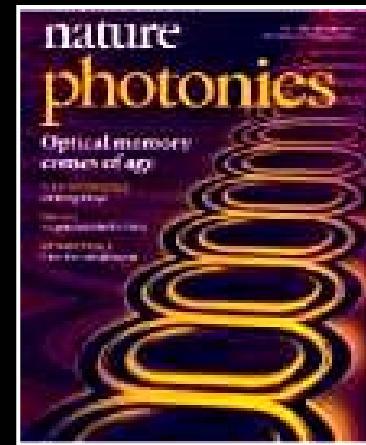
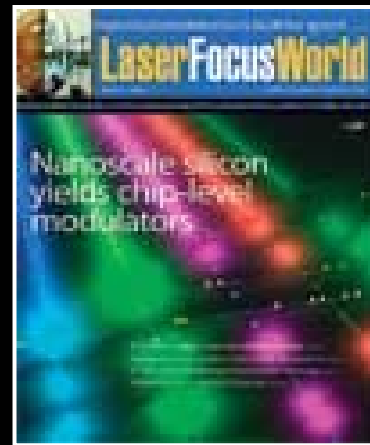
Modulator design-space



Switching by free-carrier injection



IBM Silicon Nanophotonics – Scientific Impact (2003-2010)



2005
Slow Light

2006
Si Modulator

2007
Optical Buffer

2008
Si Switch

2009
APD Detector

2010
Amplifier

2010
Ge Receiver

Journal papers:	>60 (including 5 Nature, 6 Invited)
Conferences:	>250 (including >100 Invited/Plenary)
Citation index:	>4000
Patents:	>30

Fundamental scientific work laid down solid foundation for technology development

Midway upon the journey of our life
I found myself within a forest dark,
For the straight-forward pathway had been lost.

Longfellow translation



IBM Technology Innovation Pipeline



Fundamental Research

New materials,
processes, & devices

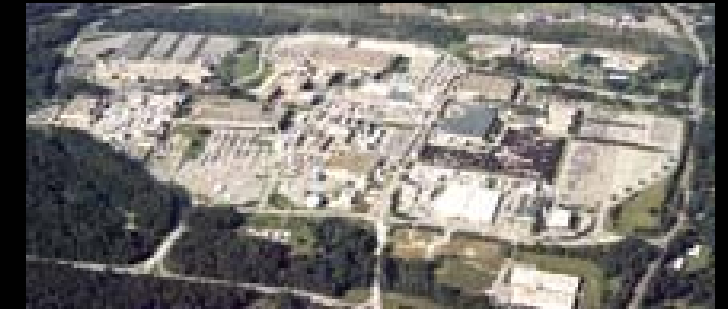
Si Nanowires

Low Dimensional
Carbon Electronics

Phase Change Memory
(PCM)

Silicon Nanophotonics

IBM Yorktown



Technology Development

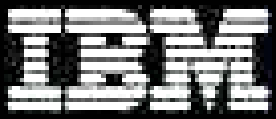
High Perf SOI eDRAM
Technology Alliance

Foundry Bulk
Technology Alliance

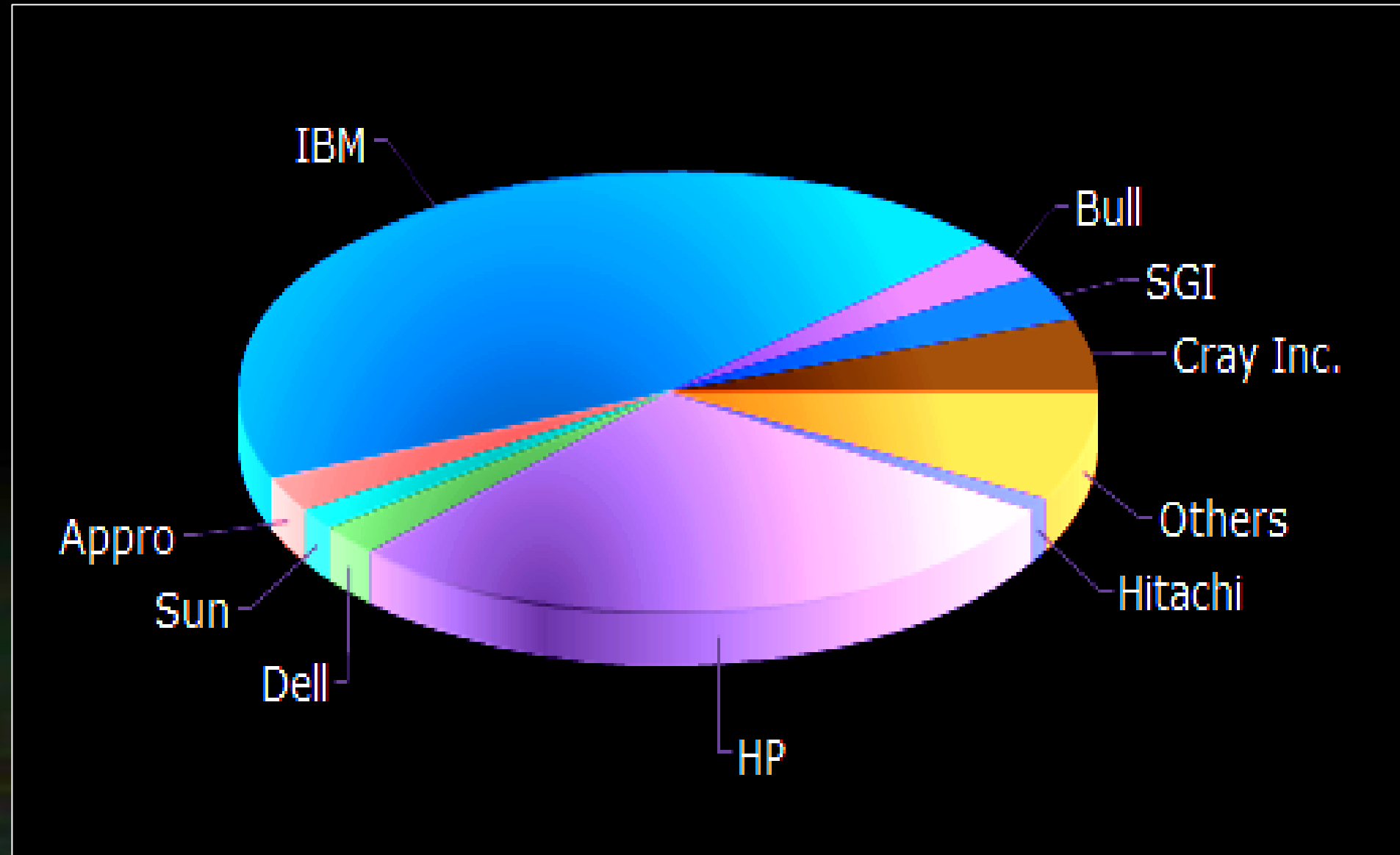
Packaging Alliances

*IBM East Fishkill
IBM Burlington
IBM Bromont
Albany Nanotech*

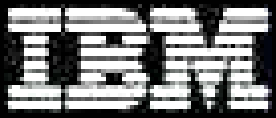
Optical Interconnects in IBM Supercomputers



www.top500.org



IBM HPC systems



MareNostrum
2006



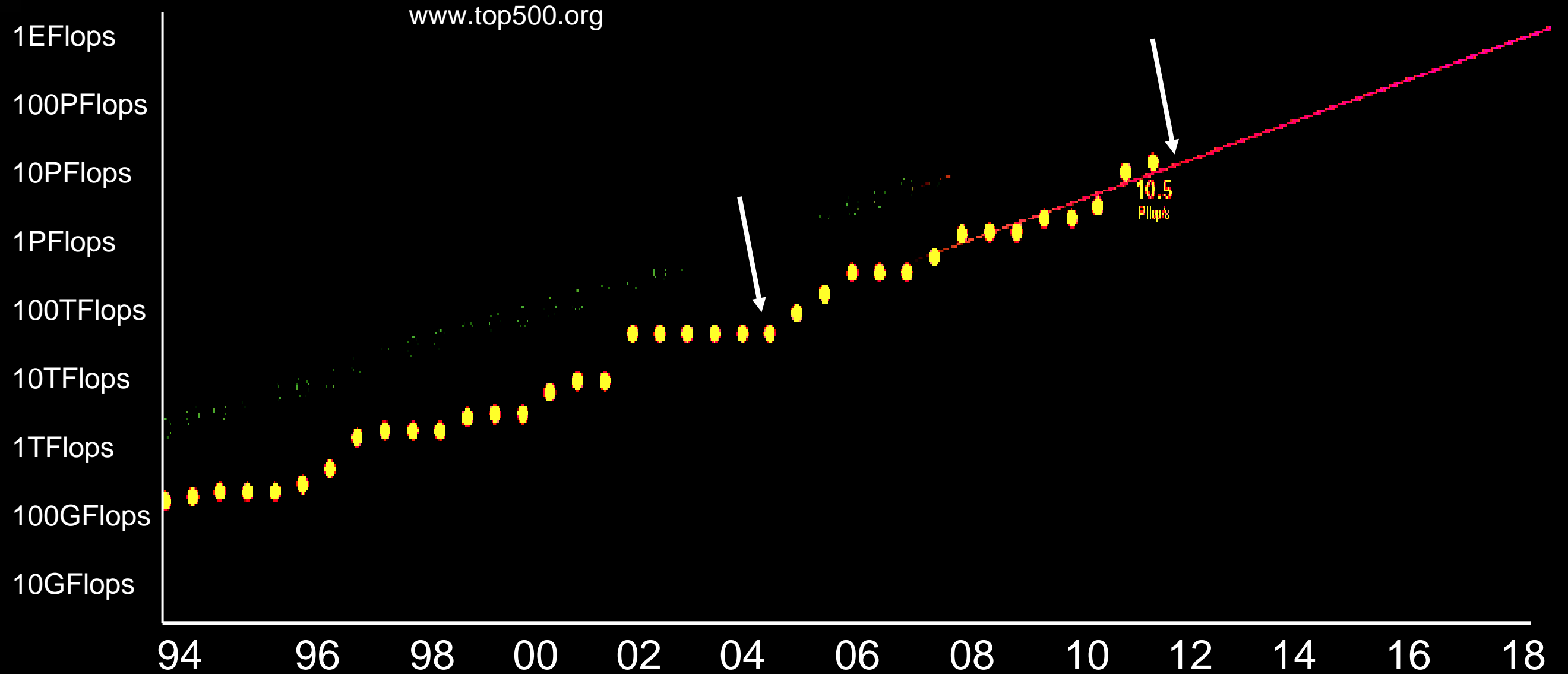
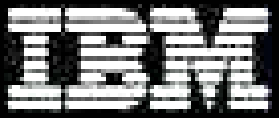
10,240 PowerPC970 processors, 90 TFlops

IBM P775 system
2011

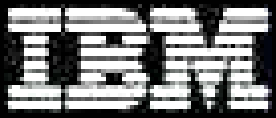


256 P7 processors, 90 TFlops

Top 500 most powerful supercomputers

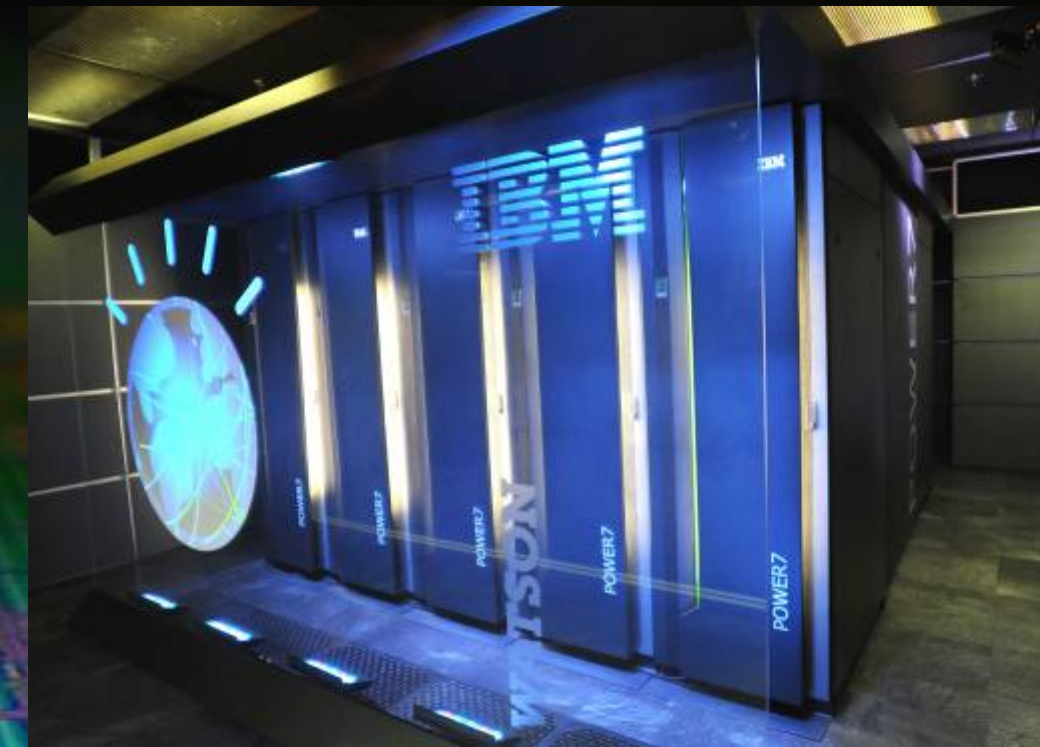


Watson – questions answering supercomputer



Medical diagnostics
Market predictions
Weather forecast

.....



From 5K to 1M fiber links in the system

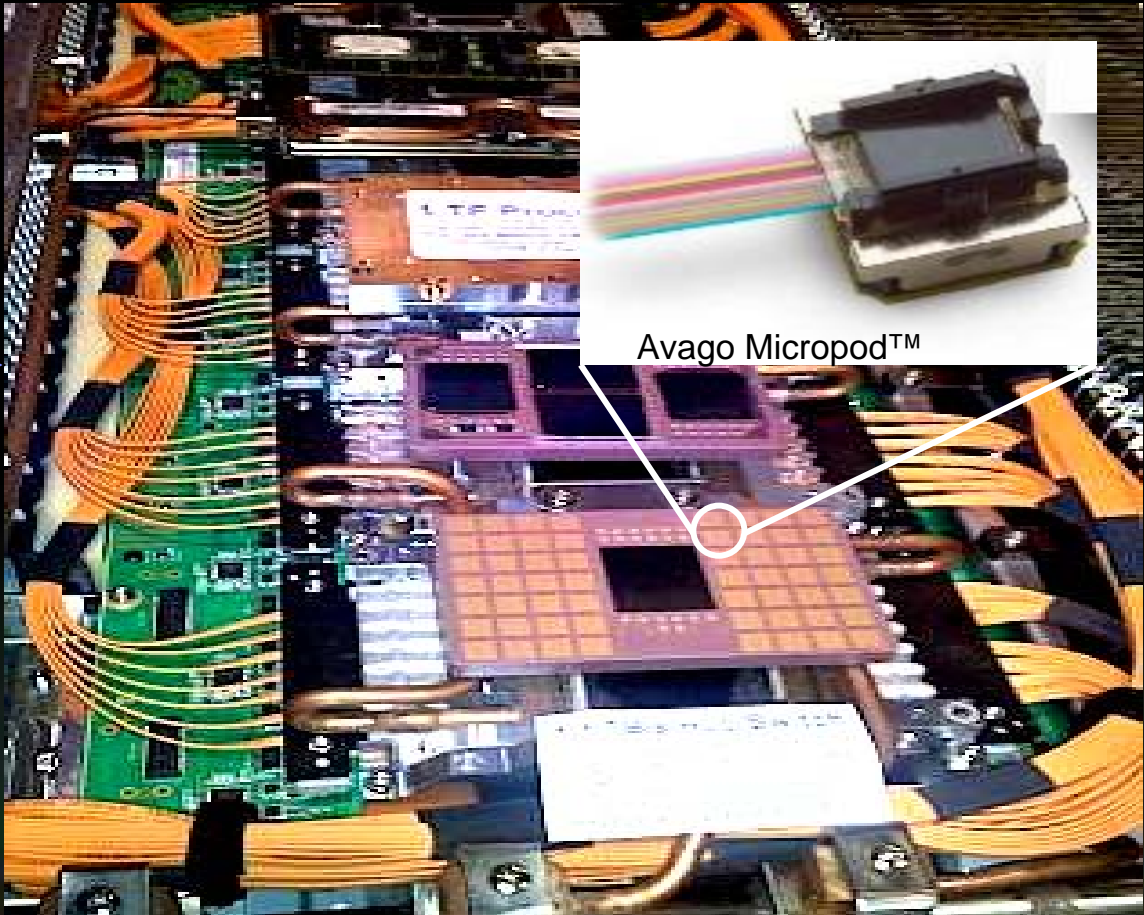
2006



MareNostrum
~5K fiber cables

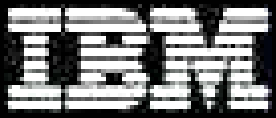


2011



P775 system
~500K fiber cables

Cost and Power per bit (unidirectional)



Year	Peak Performance	number of optical channels	Optics Power Consumption	Optics Cost
2008	1PF	48,000 (@ 5Gb/s)	50mW/Gb/s (50pJ/bit)	\$10,000 per Tb/s
2012	10PF	2×10^6 (@ 10Gb/s)	25mW/Gb/s	\$1,100 per Tb/s
2016	100PF	4×10^7 (@ 14-25 Gb/s)	5mW/Gb/s	\$170 per Tb/s
2020	1000PF (1EF)	8×10^8 (@ 25 Gb/s)	1mW/Gb/s	\$25 per Tb/s

Acknowledgment: A. Benner, J.Kash

■ Future directions for optical cables:

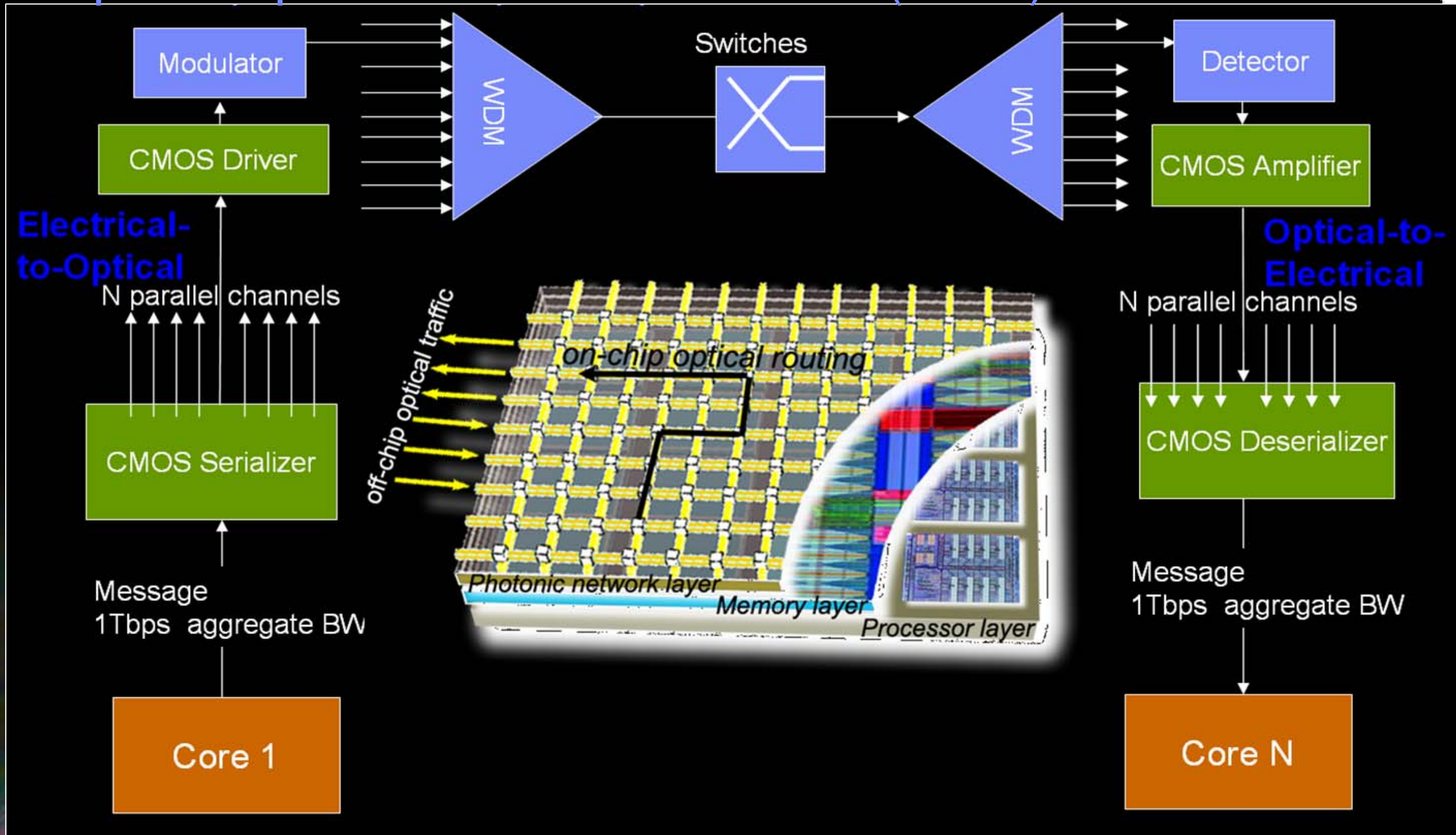
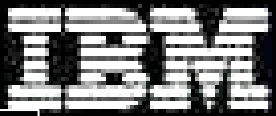
- Lower cost (reducing >60%/year)
- Much more BW (increasing >210%/year)
- Much lower power (improving >45%/year)

■ New technologies needed

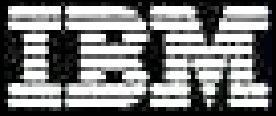


Follow the YBR

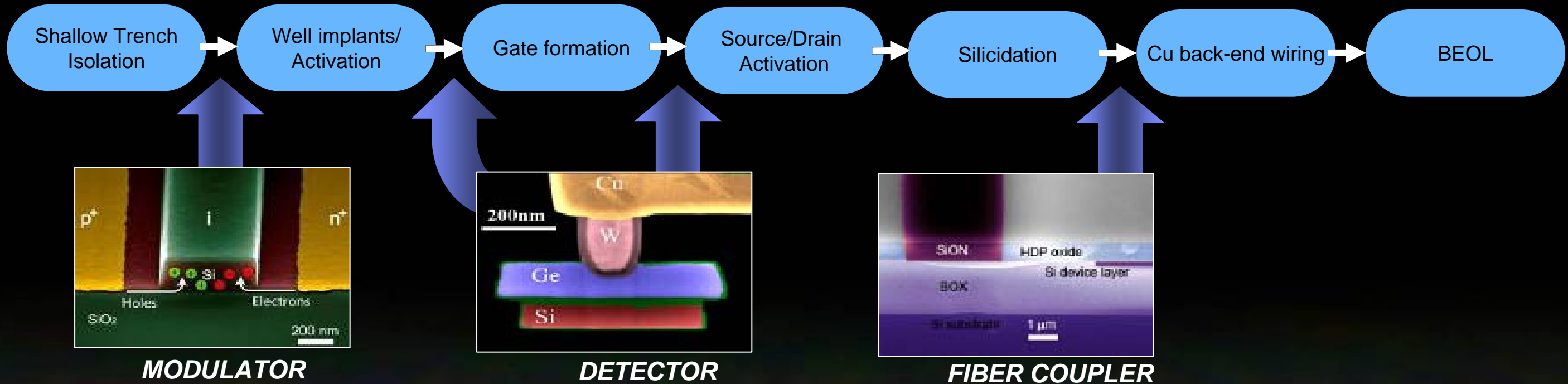
Off-Chip Nanophotonics Interconnects (2006)



IBM manufacturing process integration



Front-end photonics integration



- ✓ Most of the mask levels and processing modules are shared
- ✓ Minimal additional photonics modules added

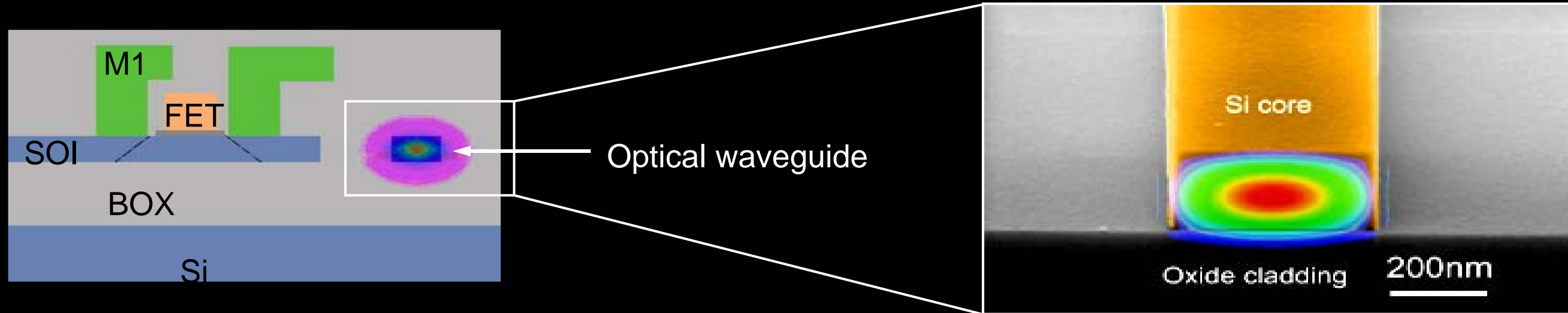
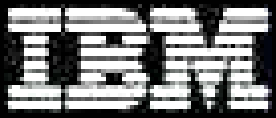
W.Green, et al, SEMICON Japan 2010;

S.Assefa et al OFC 2011

IBM press-release Dec.2010

Over 40 base patents

CMOS front-end monolithic Nanophotonics integration



→ Nanophotonics sharing Si layer with FET body

Advantages:

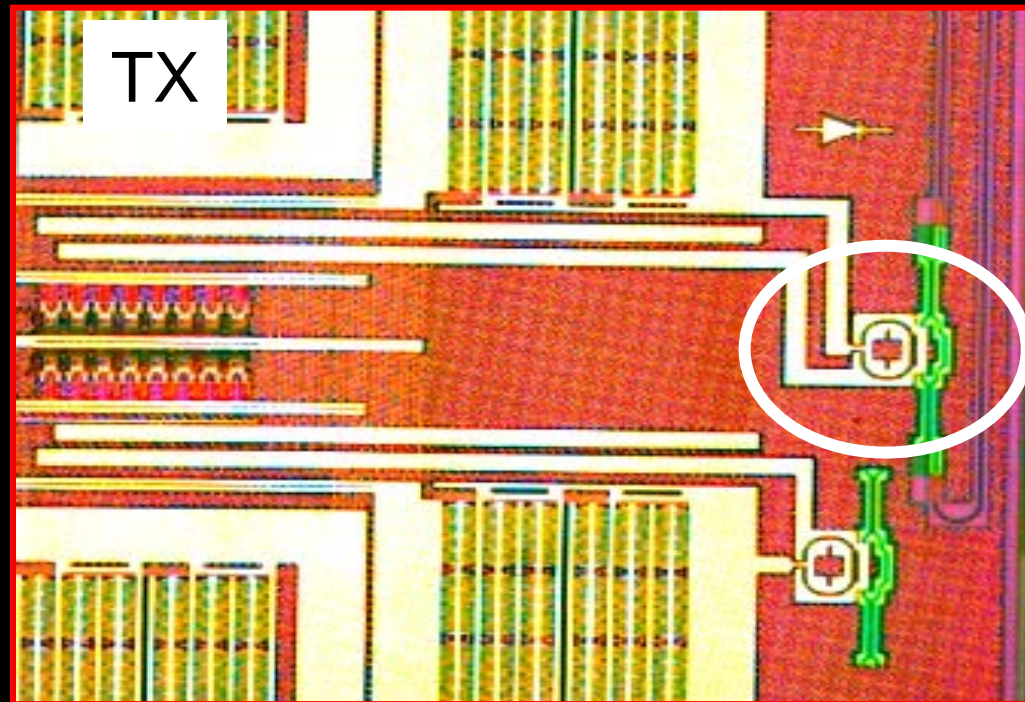
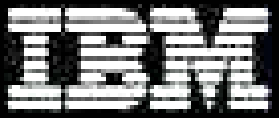
- ✓ Deeply scaled Nanophotonics
- ✓ Most dense integration with CMOS
- ✓ Ultra-low power optical interconnects
- ✓ Same mask set, standard processing
- ✓ Same design environment (e.g. Cadence)
- ✓ Same EDA tools and design flow
- ✓ In-line system-level testing

$\lambda_1 \dots \lambda_6$

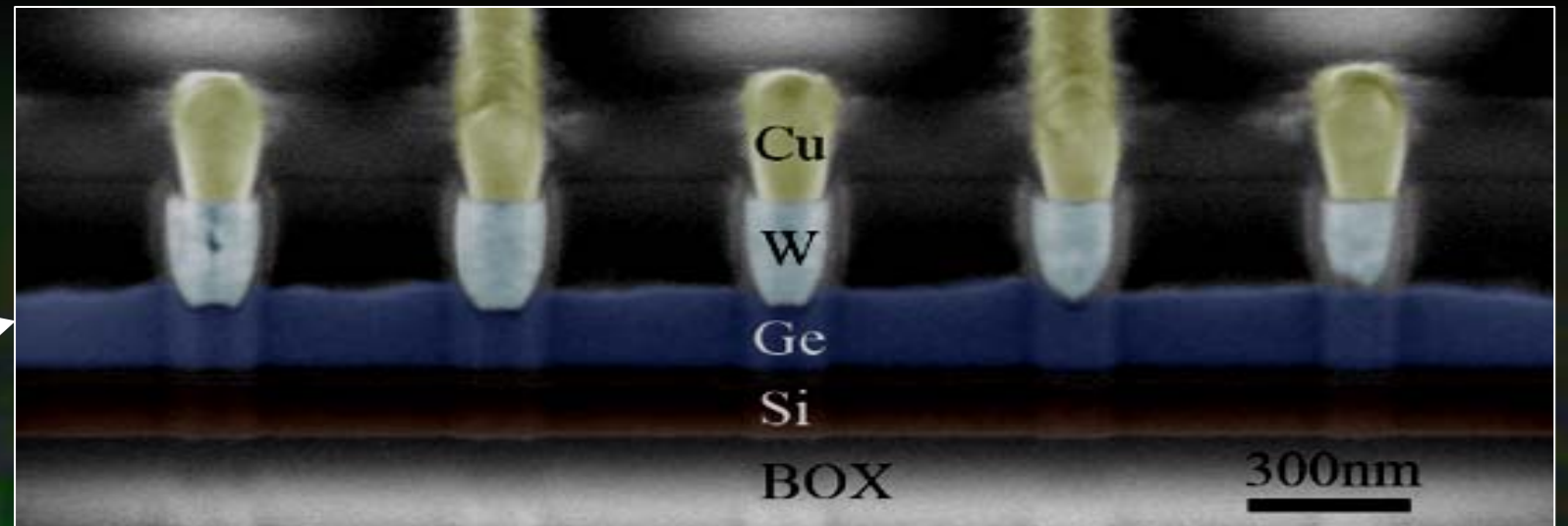
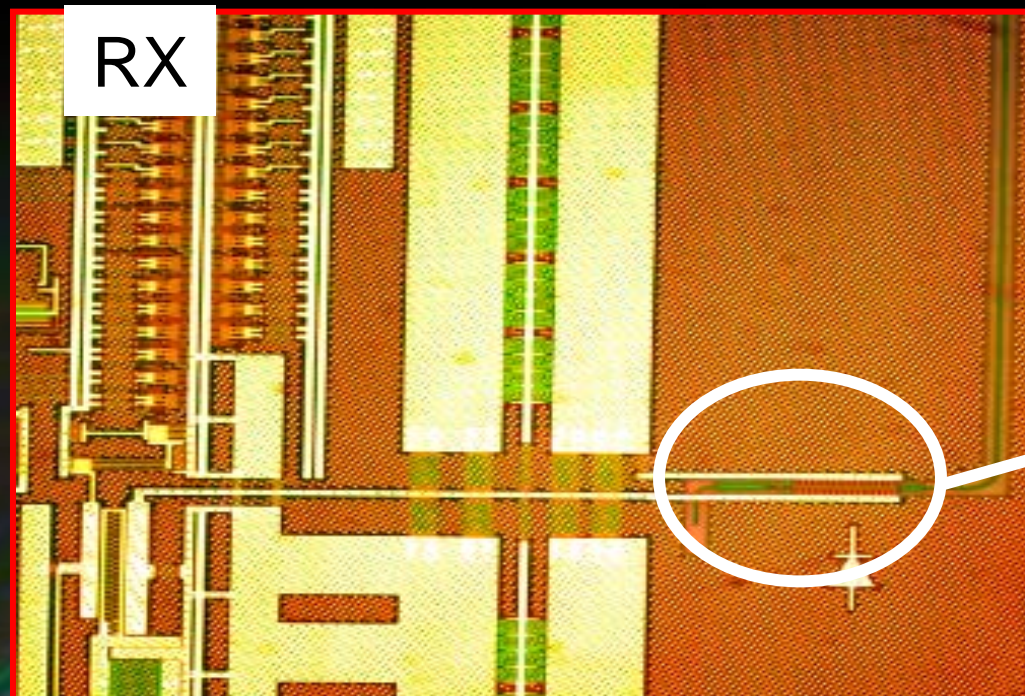


6-channel WDM

SNIPER hardware includes complete optical link



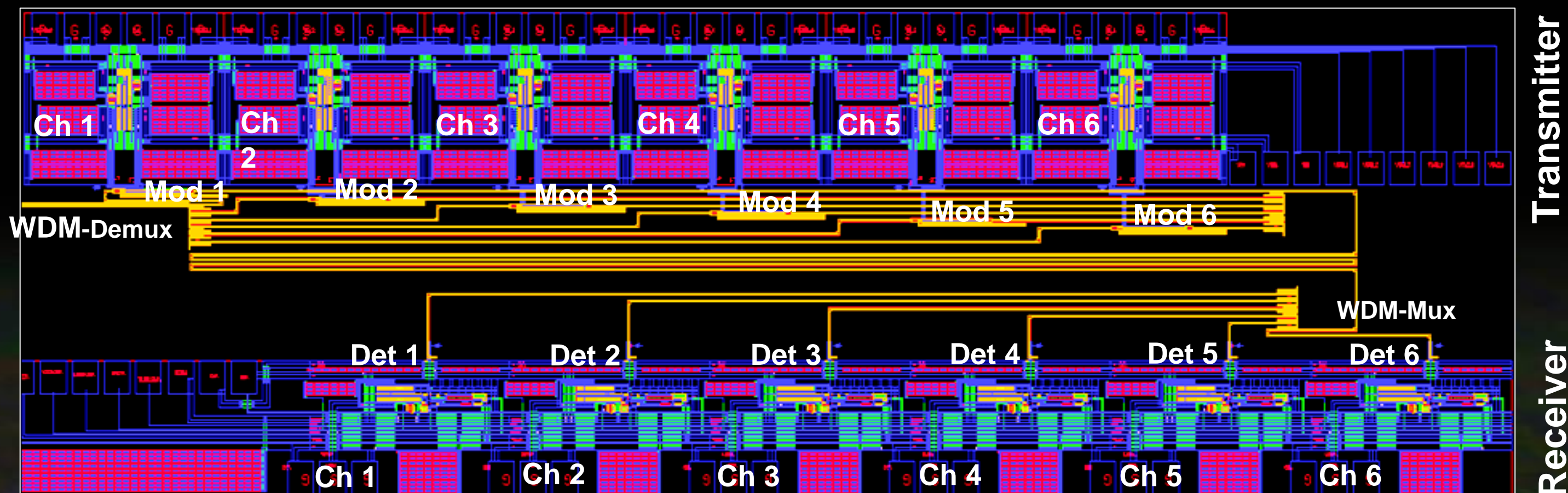
Modulator (25Gbps, 32Gbps option in testing)



Ge Detector (25Gbps, 40Gbps option in testing)

Co-design of Photonics and CMOS

- Library of photonic components
- Photonics-enabled design rules
- Photonics-enabled DRC, LVS, modeling

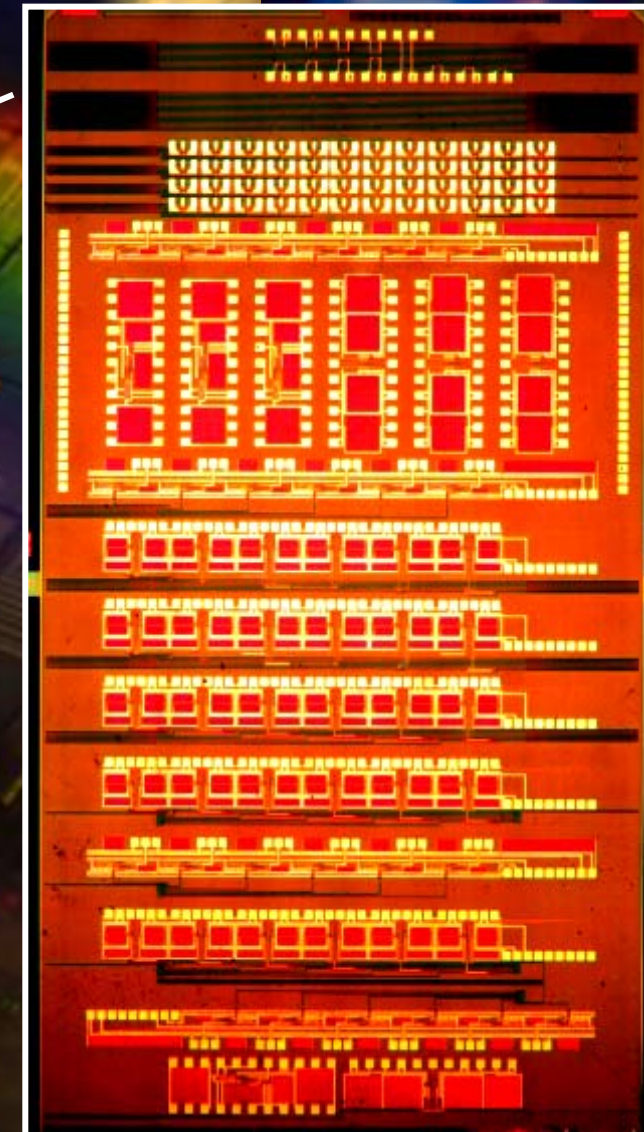
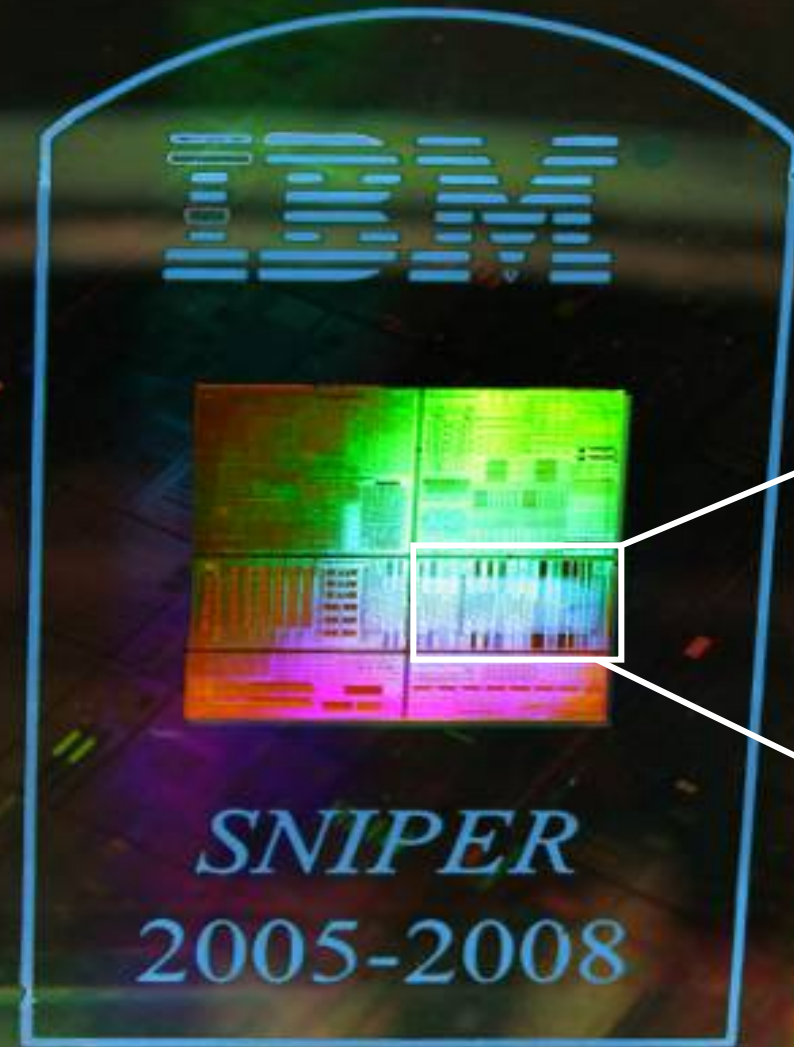


✓ Allows to layout complex CMOS and Nanophotonics circuits

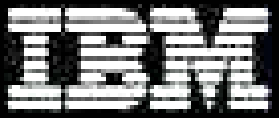
Silicon CMOS-Integrated Nanophotonics (SCIN) Technology

- ✓ CMOS FEOL integrated (Ge-first prior to activation)
- ✓ Small litho variations - active tuning not required
- ✓ 0.5 mm² per XCVR channel

William Green
Solomon Assefa
Alexander Rylyakov
Clint Schow
Folkert Horst



Road mapping

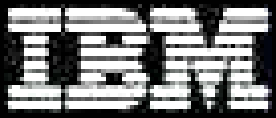


Applications \leftrightarrow Products
 \leftrightarrow Markets \leftrightarrow NRE \leftrightarrow
 \leftrightarrow Pricing \leftrightarrow ROI

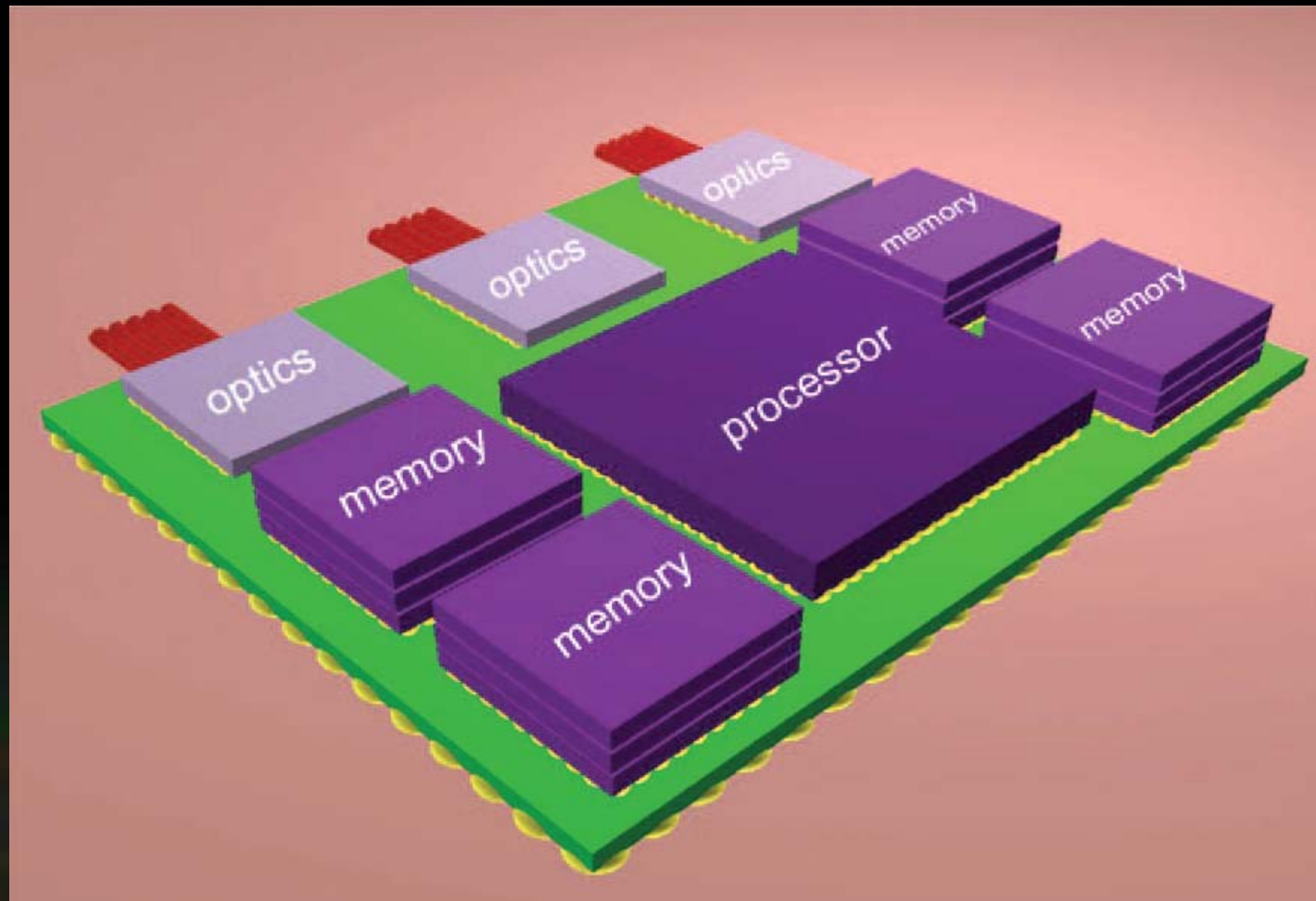


Product \leftrightarrow Performance \leftrightarrow
Top-level design \leftrightarrow
Component specifications \leftrightarrow
 \leftrightarrow Design choice \leftrightarrow
Manufacturability \leftrightarrow Reliability
 \leftrightarrow COST, COST , COST

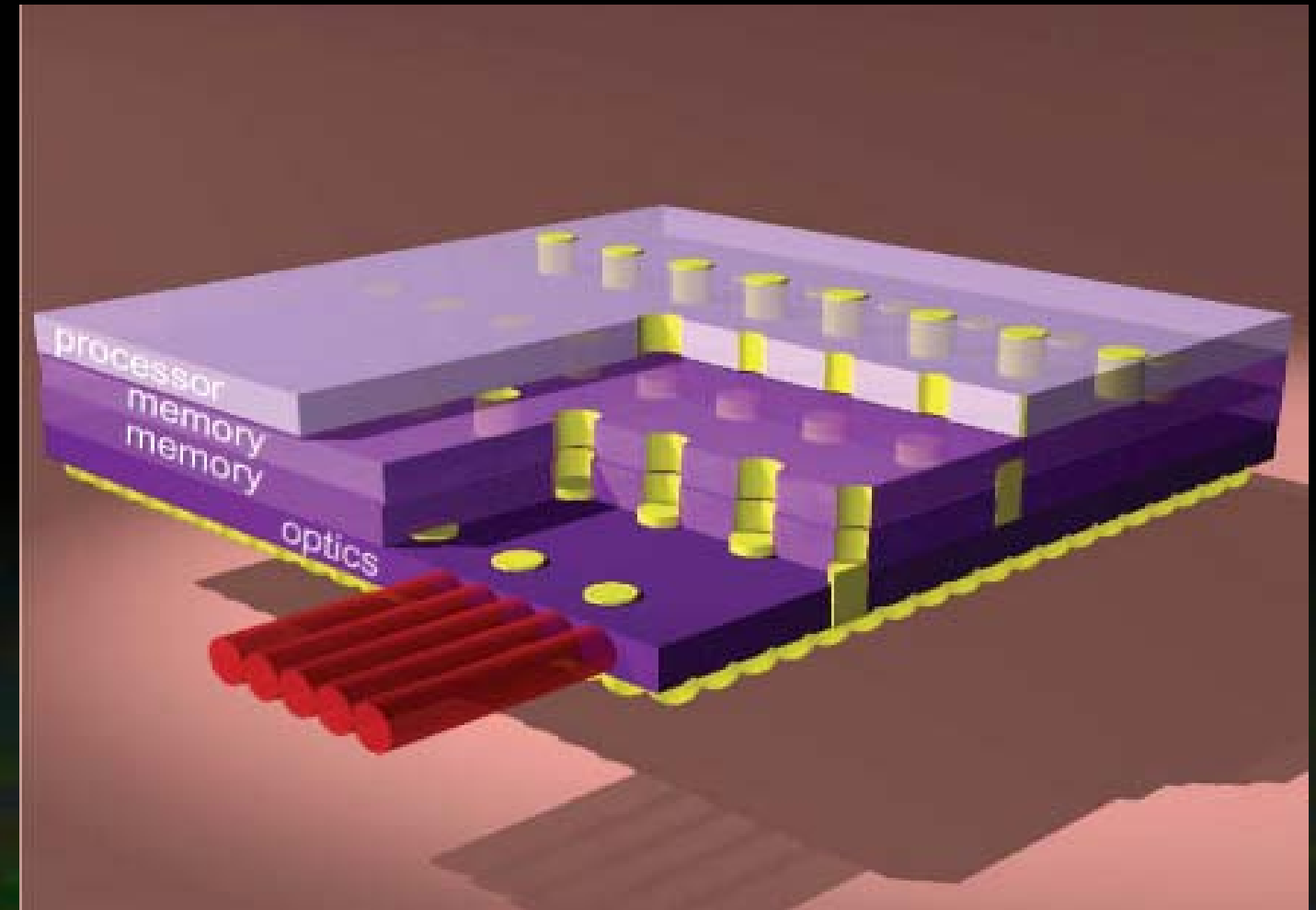
Map of the road



Circa 2015

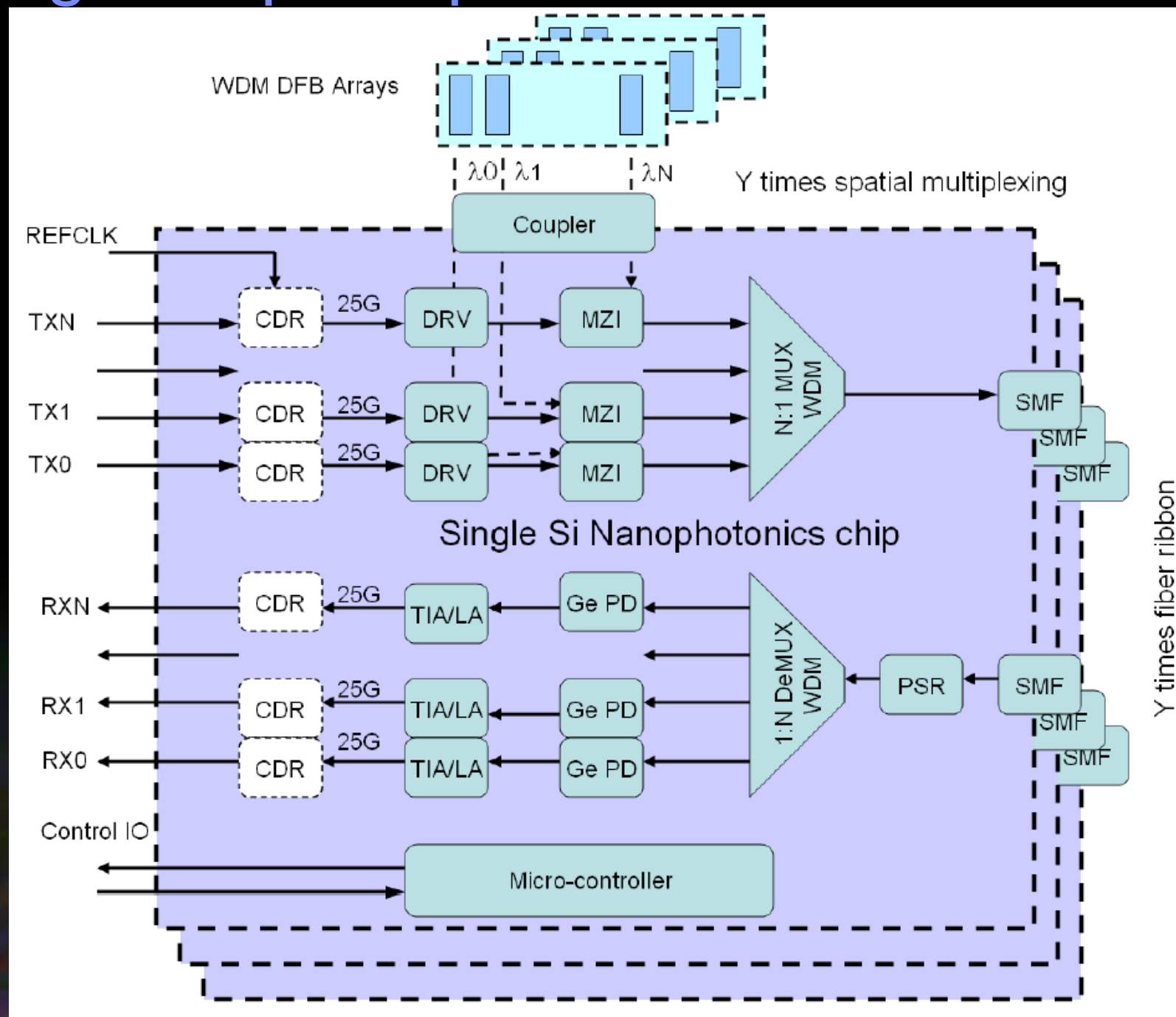


Circa 2020



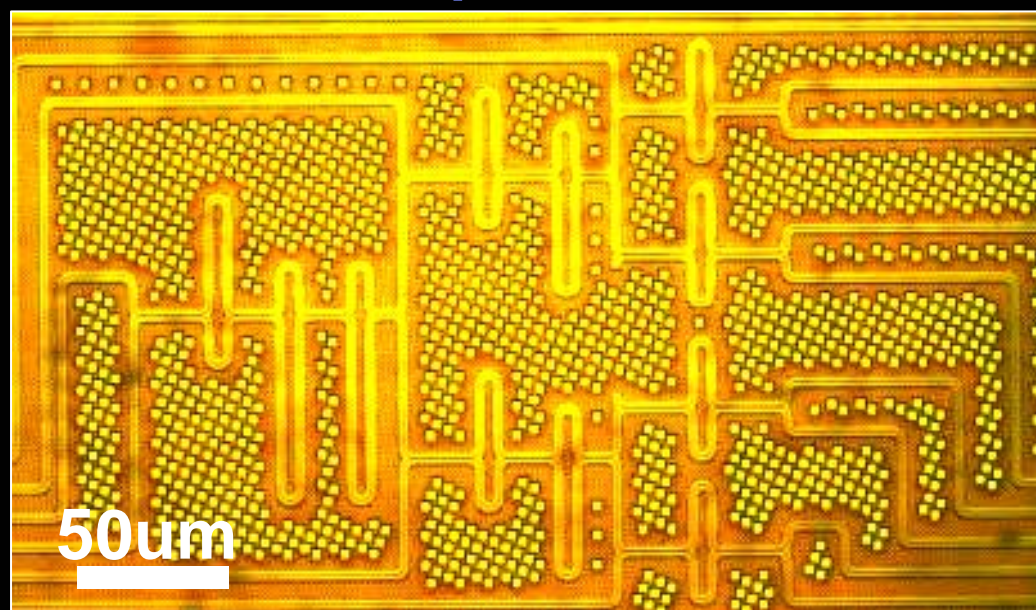
“Technologies for Exascale systems”, P. Coteus, J.Knickerbocker, C. Lam, and Y. Vlasov
IBM Journ. R&D, 55, No.5, 2011

Concept of a single-chip 1Tbps transceiver

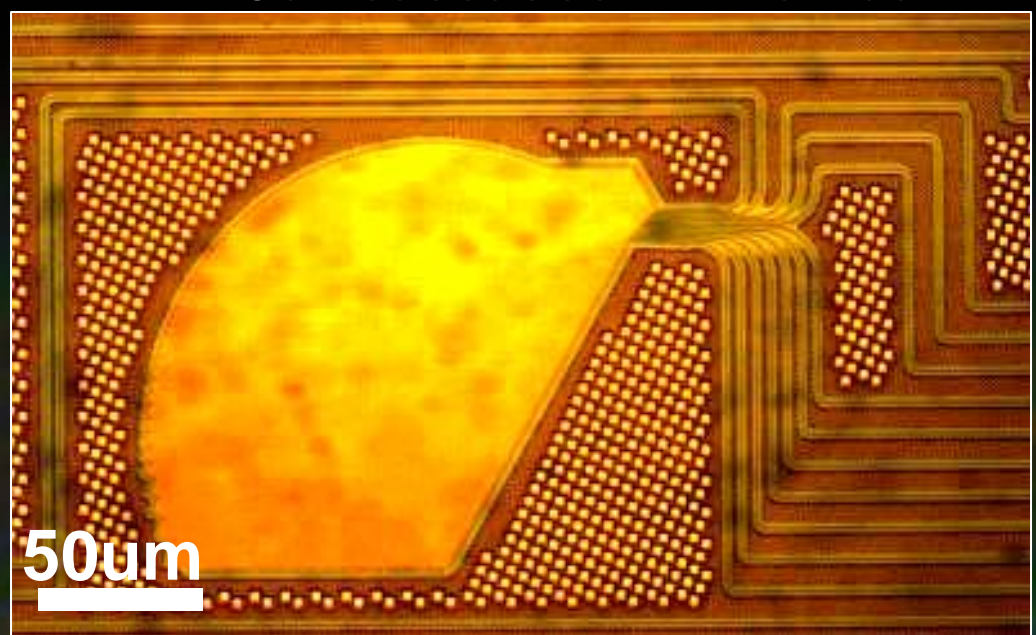


Y. Vlasov "Si Nanophotonics for Computercom beyond 100G" *IEEE Comm. Mag.*, March 2012,

WDM multiplexers

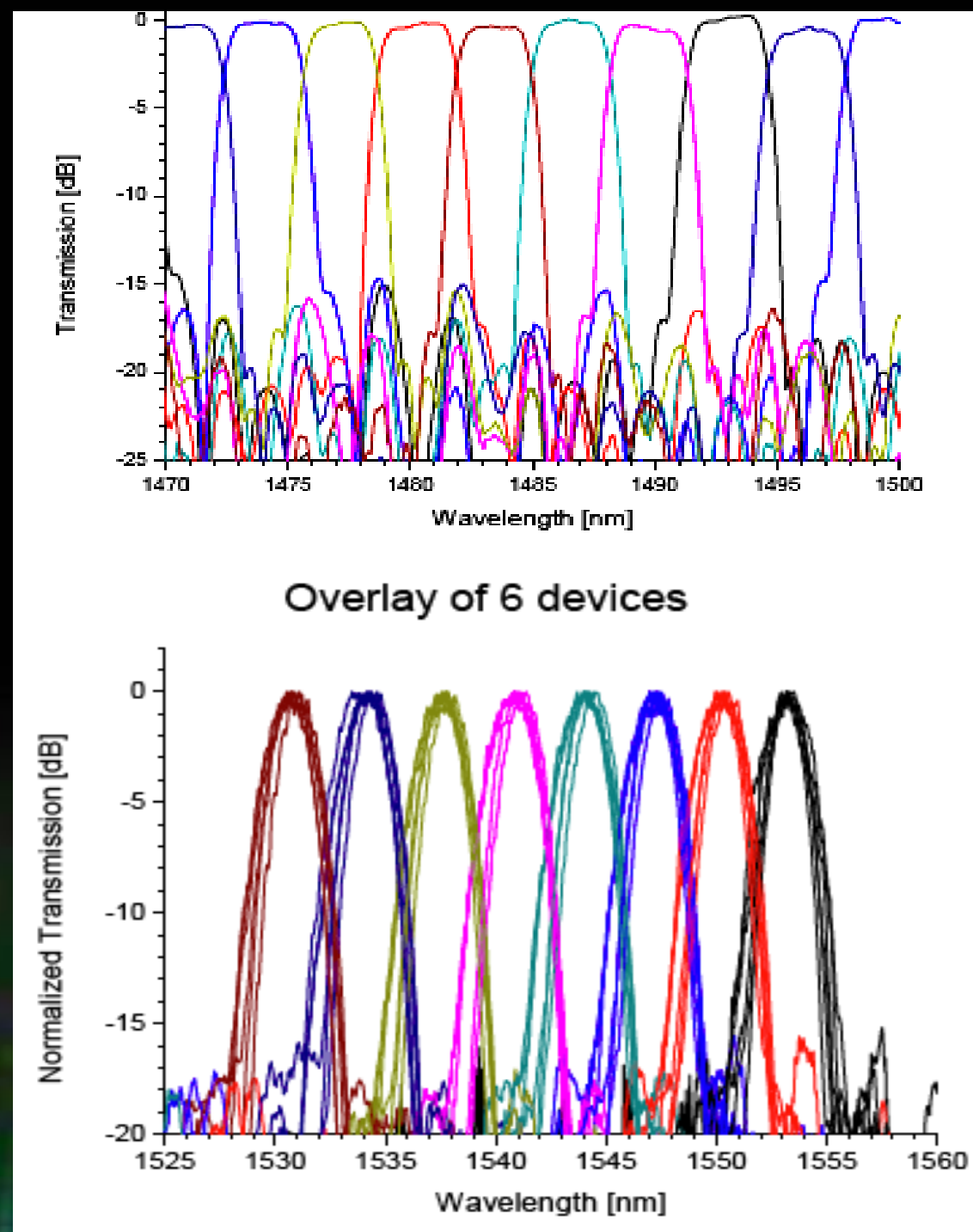


8ch cascaded MZI lattice



10ch Echelle grating

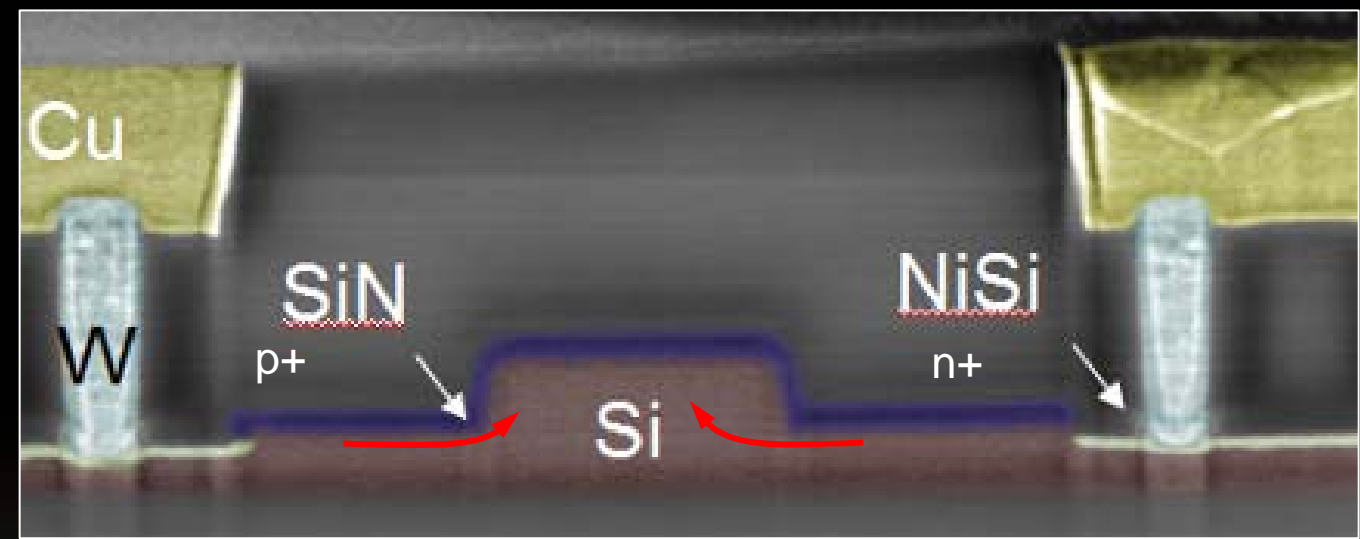
Folkert Horst (IBM Zurich) Invited talk OFC 2011



Modulator

Need 5pC for PI phase shift in Si waveguide

Capacitance per unit length is the key → PN-junction engineering



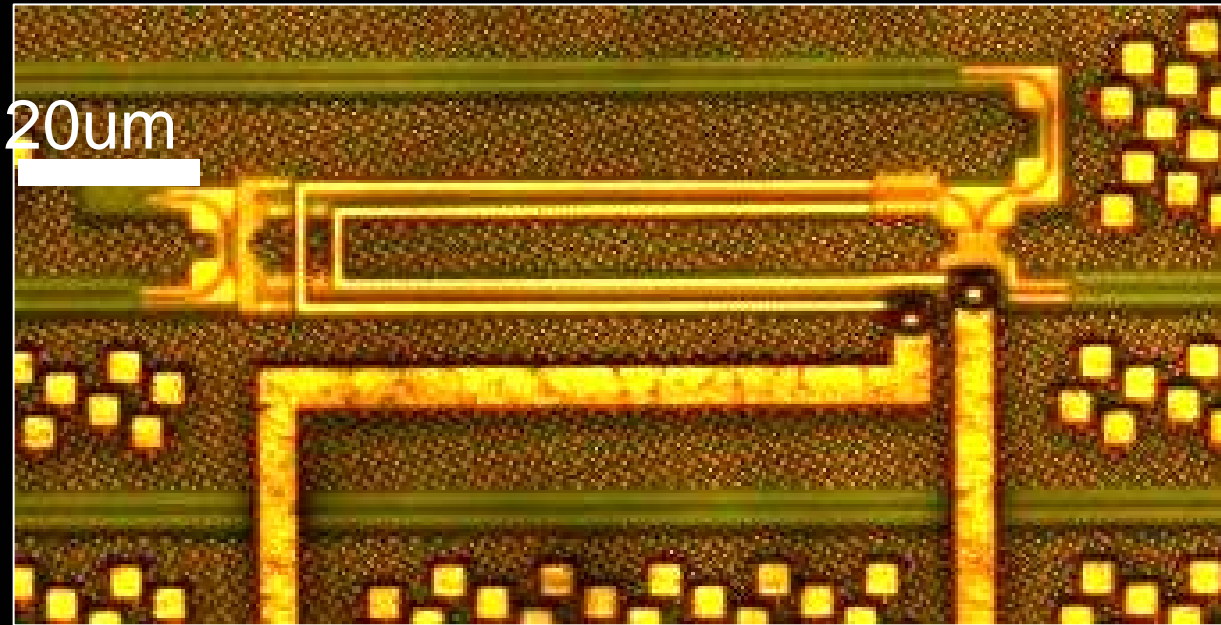
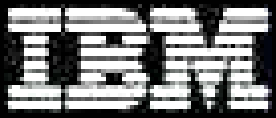
PN diode in reverse bias

A. Liu et al., Optics Express **15**, 660 (2007).
D. Marris-Morini et al., Optics Express **16**, 334 (2008).
S. J. Spector et al., Optics Express **16**, 11027 (2008).
J. W. Park et al., Optics Express **17**, 15520 (2009).
P. Dong et al., Optics Express **17**, 22484 (2009).
T.-Y. Liow et al., JSTQuantum Electron. **16**, 307 (2010).
J. Fujikata et al., OFC 2010
D. M. Gill et al., JST. Quantum Electron. **16**, 45 (2010).
M. R. Watts et al., JST Quantum Electron. **16**, 159 (2010).

J. Rosenberg et al, PDP CLEO 2011, May 2011

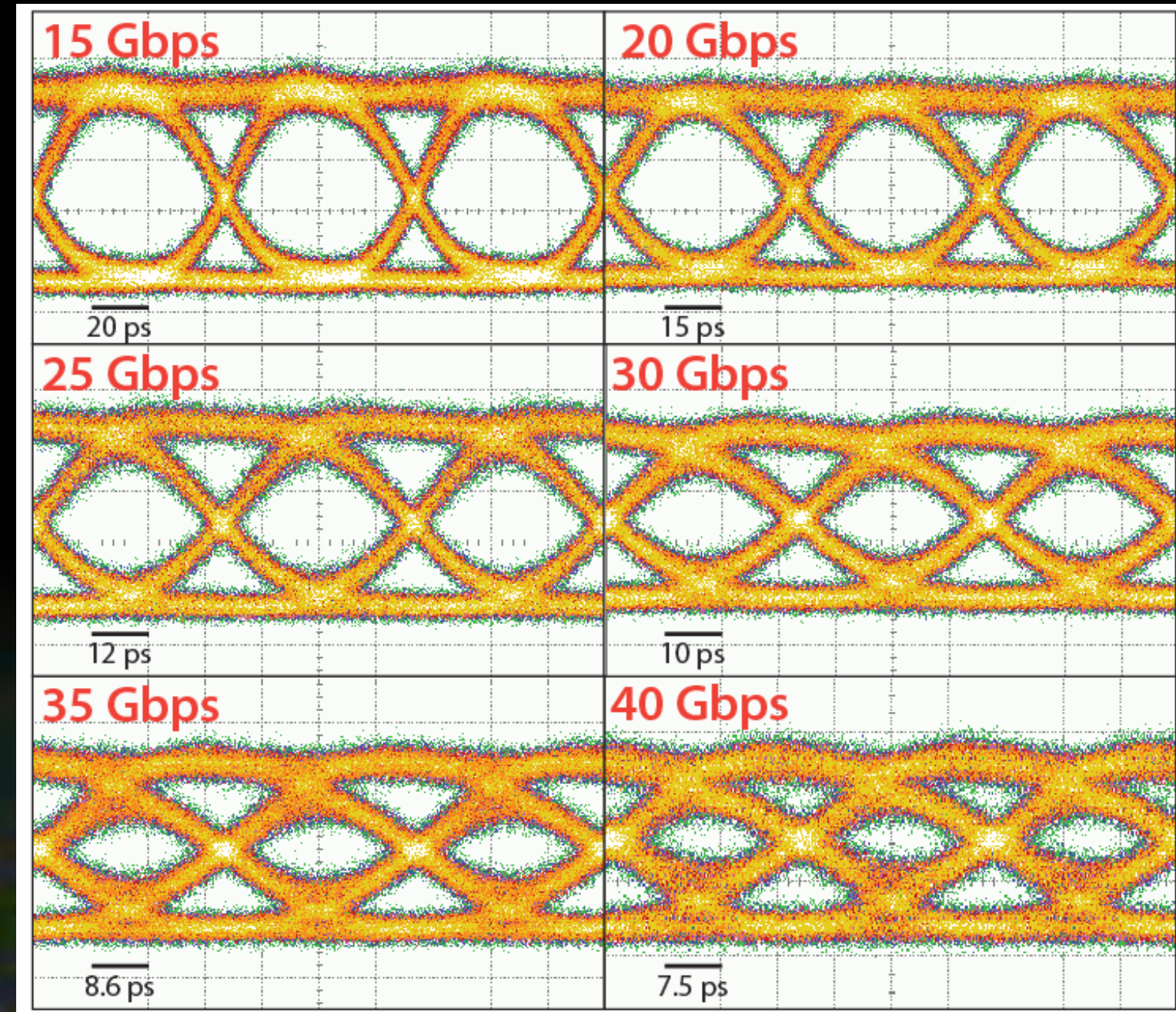
	$V_{\pi} \cdot L$
Intel	4 V·cm
CNRS/CEA-LETI	5 V·cm
Lincoln Labs/MIT	4 V·cm
IME A*STAR PN	2.5 V·cm
Bell Labs/BAE Systems	2 V·cm
ETRI, South Korea	1.8 V·cm
Kotura/Oracle	1.5 V·cm
Sandia Labs	1 V·cm
IME A*STAR MOSCAP	0.5-0.67 V·cm
IBM*	0.6 V·cm

Silicon ring modulator

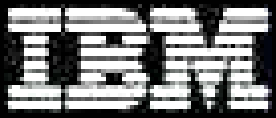


Die photo

- ✓ Insertion loss 1dB
- ✓ Extinction ratio 3-4dB
- ✓ 130fF; 10 Ω
- ✓ CMOS compatible voltages
- ✓ Consumes 84fJ/bit at 25Gb/s



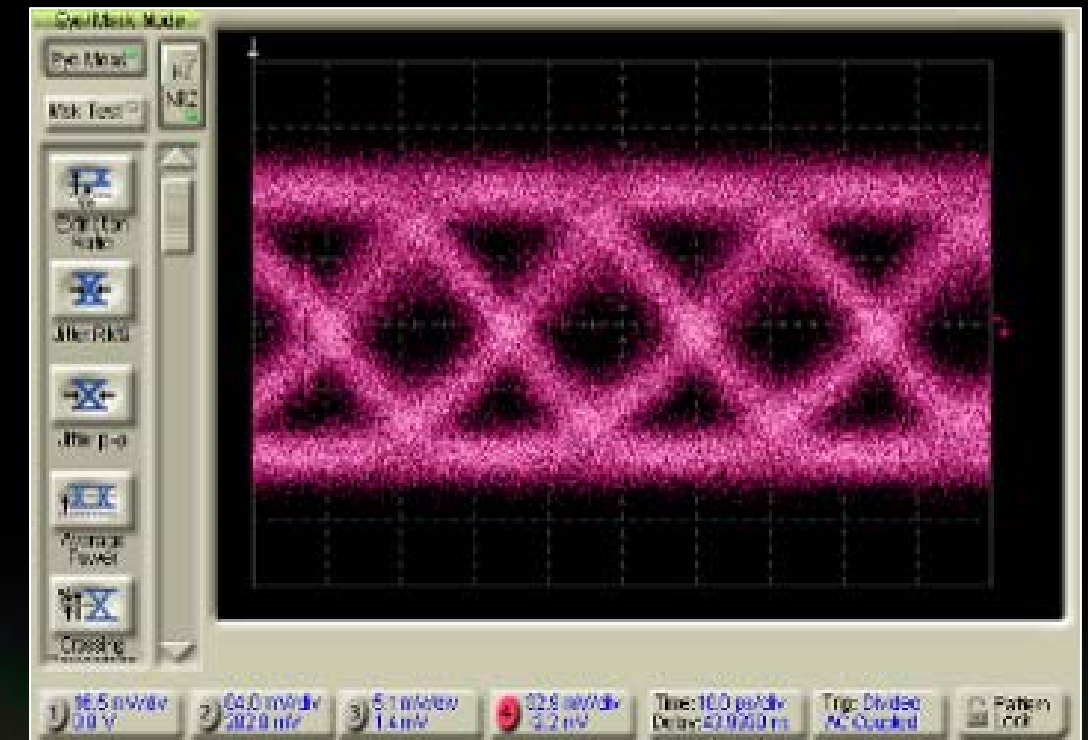
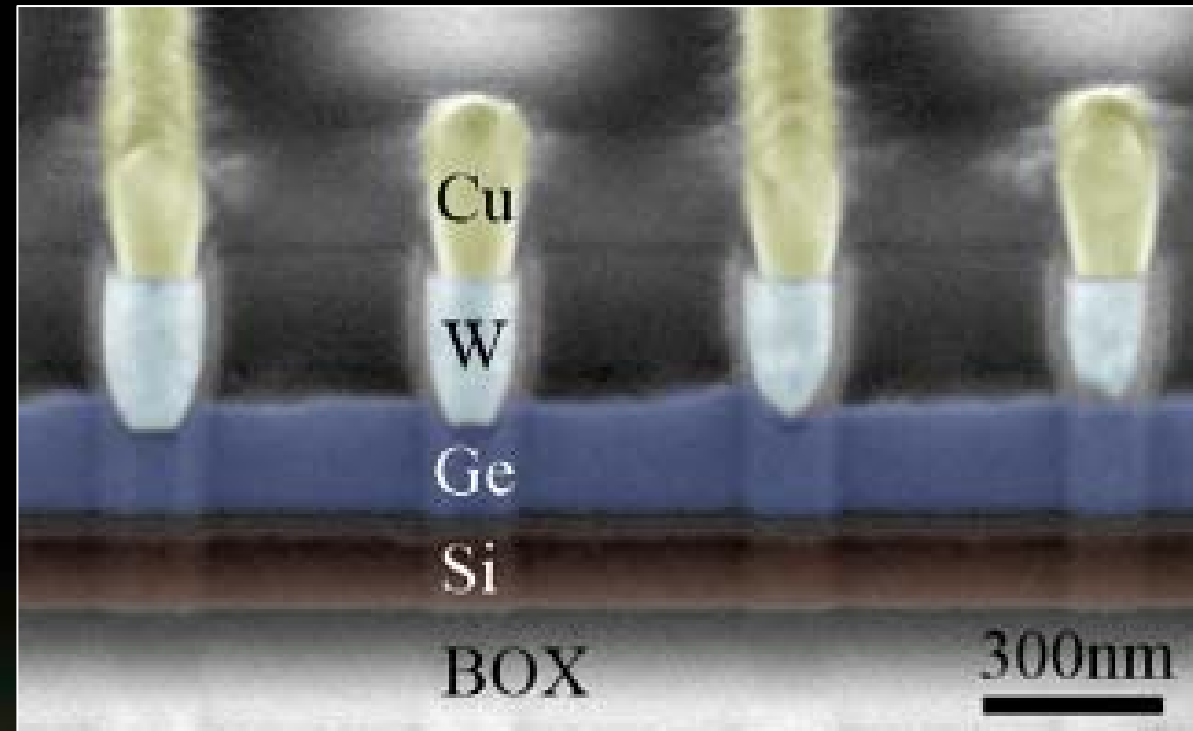
Ge waveguide photodetector



Die photo

Design

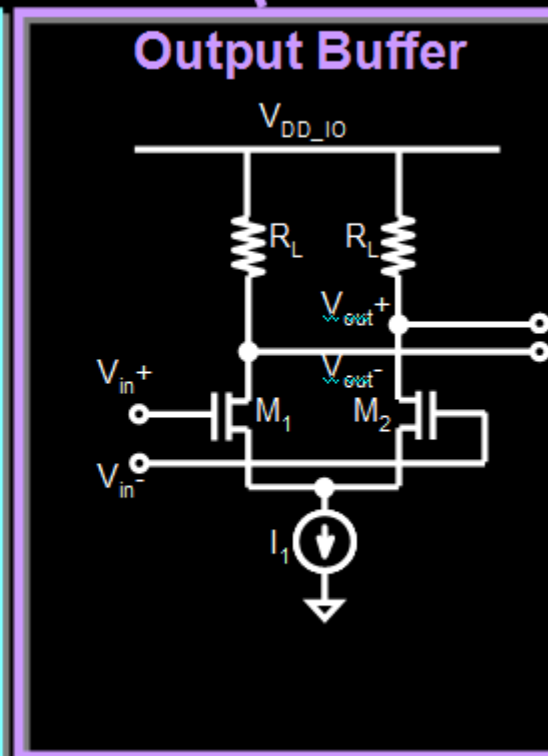
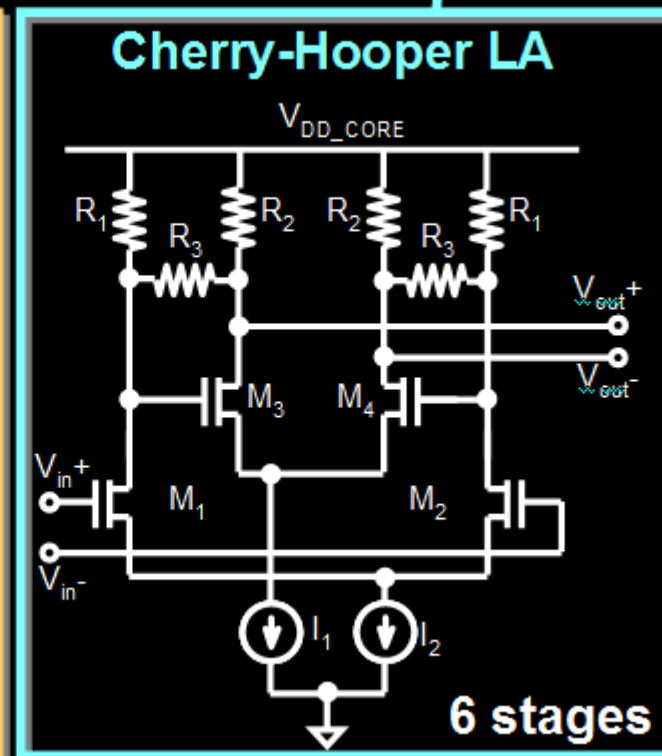
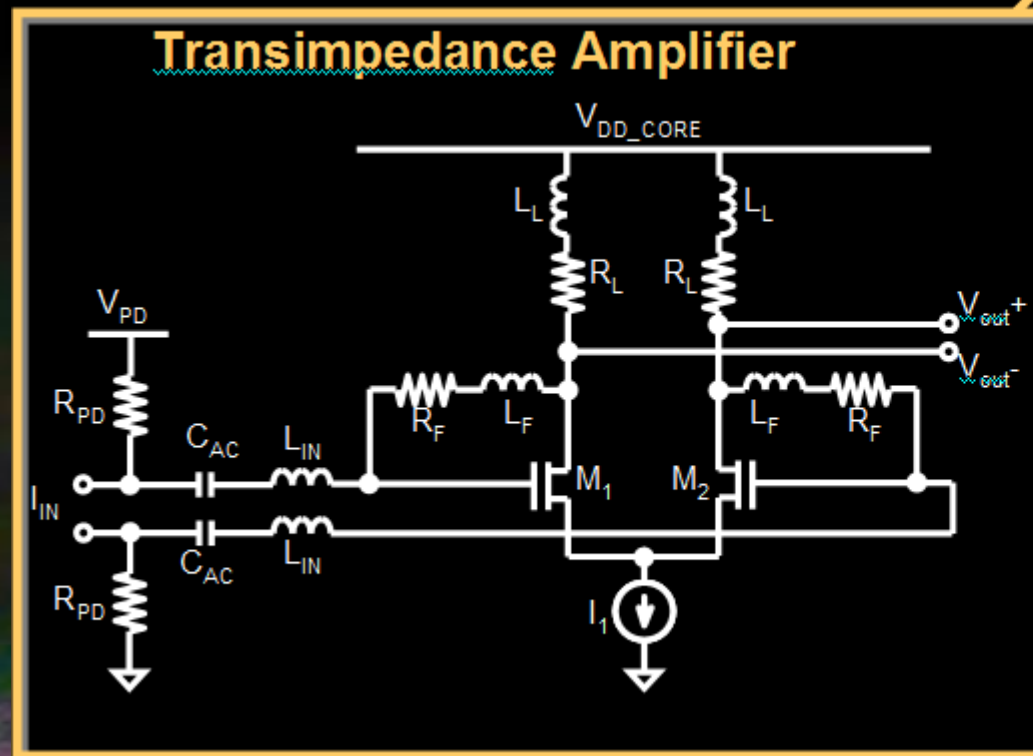
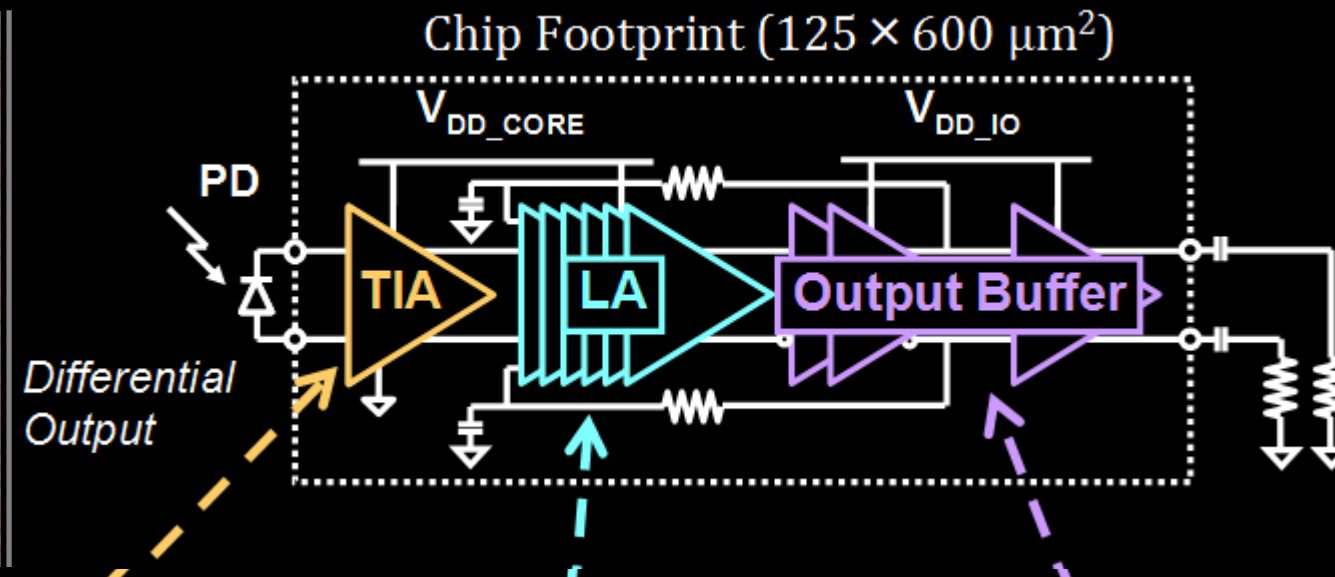
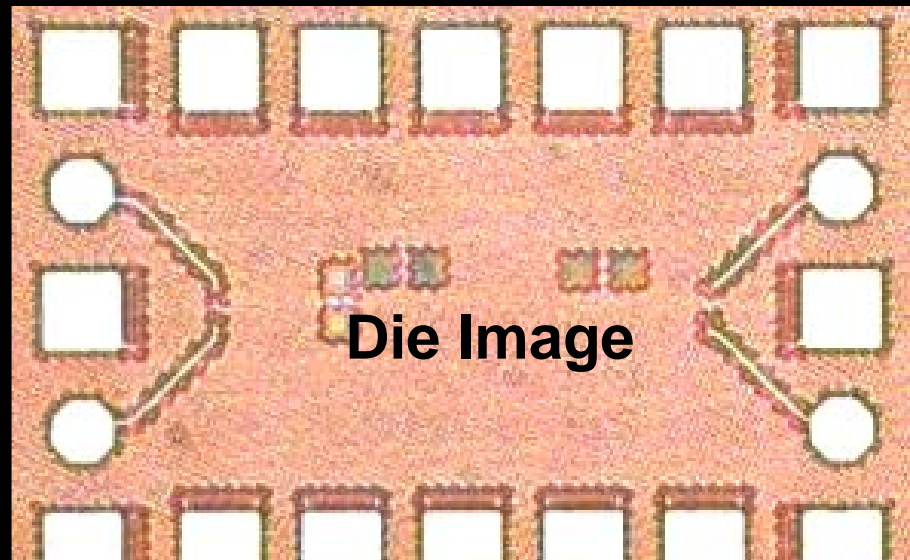
Performance



- ✓ Ge detector integrated with CMOS Circuitry
- ✓ 20um long
- ✓ 40GHz bandwidth with CMOS bias voltages
- ✓ 0.5A/W responsivity at 1.3um and 1.5um

S.Assefa et al, Nature, March 2010
S.Assefa et al, OE, April 2010
S.Assefa et al, JSTQE, September 2010

IBM Bulk 90-nm CMOS Receiver Analog IC



Progress 2010-2011

Oct. 2010

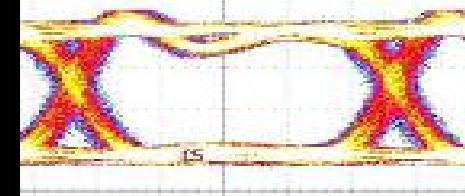
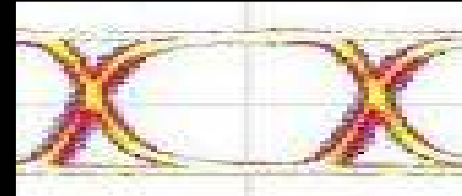
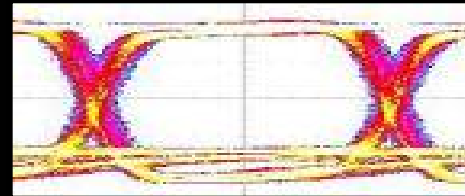
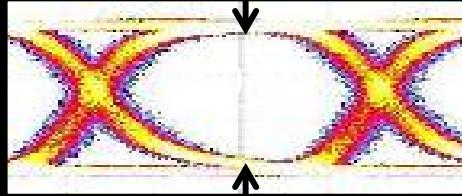
Jan 2011

Mar 2011

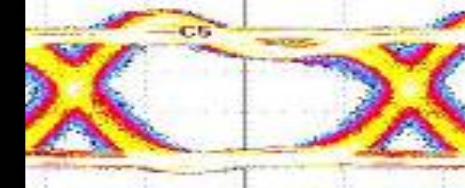
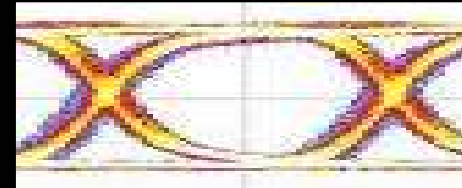
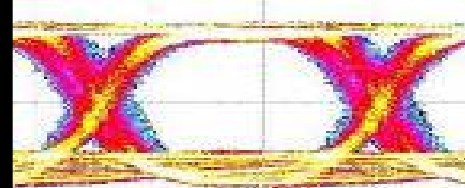
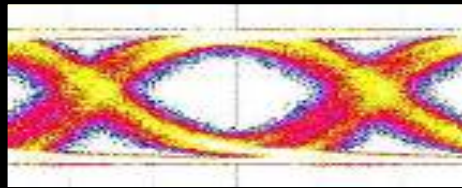
Sep 2011

Oct 2011

10 Gb/s

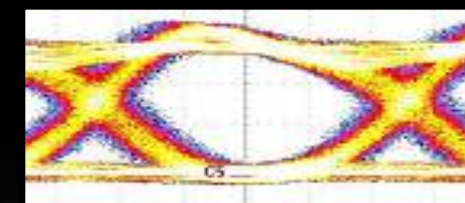
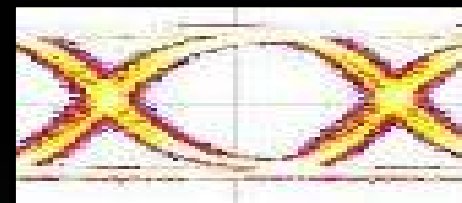
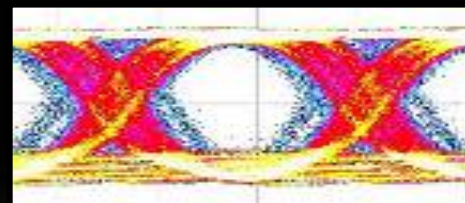


15 Gb/s



20 Gb/s

15Gbps
4.7pJ/bit
-8dBm

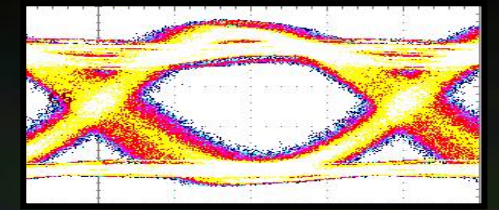
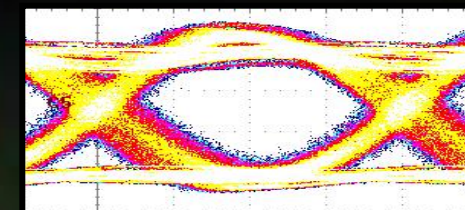


Assefa et al OFC 2011

25 Gb/s

20Gbps
6.9 pJ/bit
-7.1dBm

20Gbps
5.4 pJ/bit
-12dBm



Assefa et al OFC 2011 PDP

28 Gb/s

25Gbps
4.84 pJ/bit
-10.2dBm



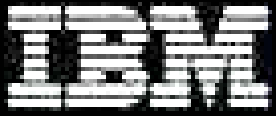
Assefa et al CLEO 2011

H.Pan et al OFC 2012

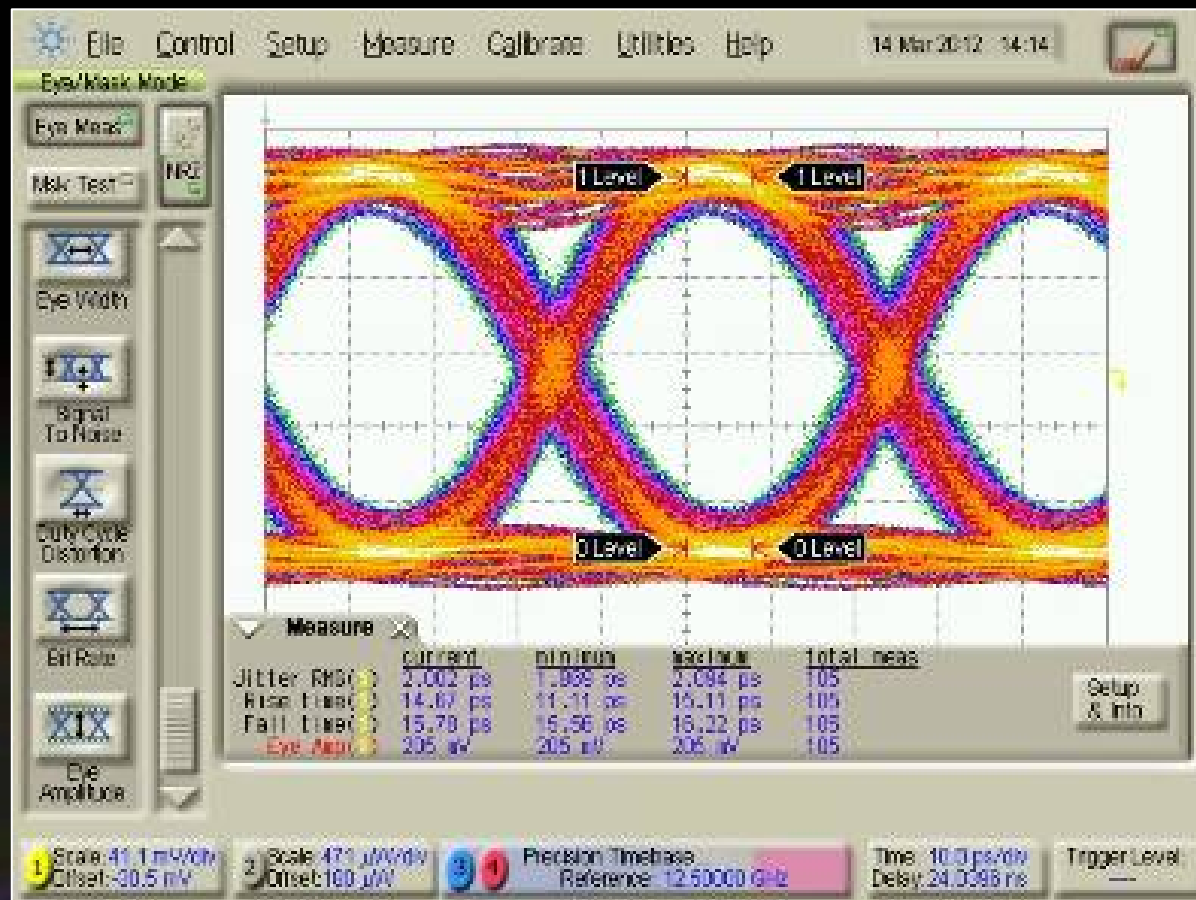
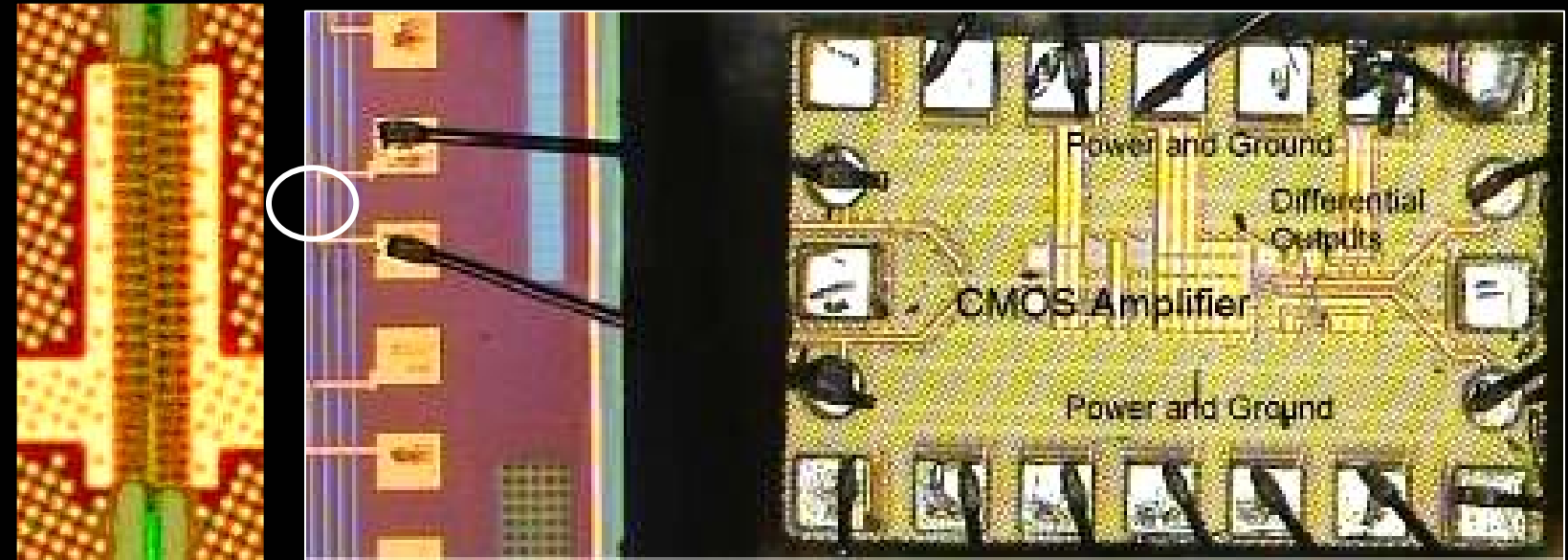
28Gbps
4.6 pJ/bit
-9dBm

300 mVpp differential output

Receiver



- CMOS die 90nm
- Ge WG PD die
- wire bonded

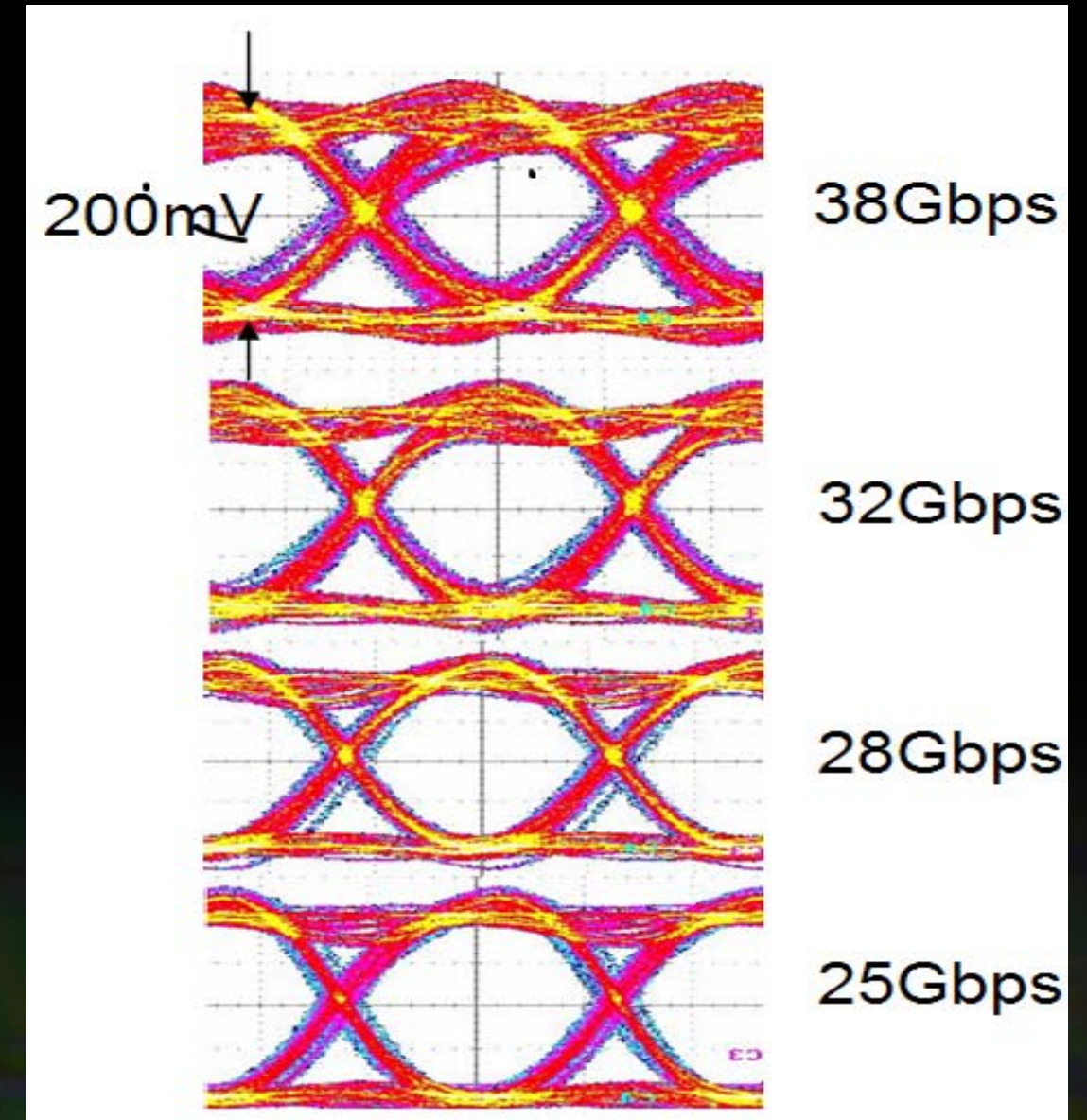
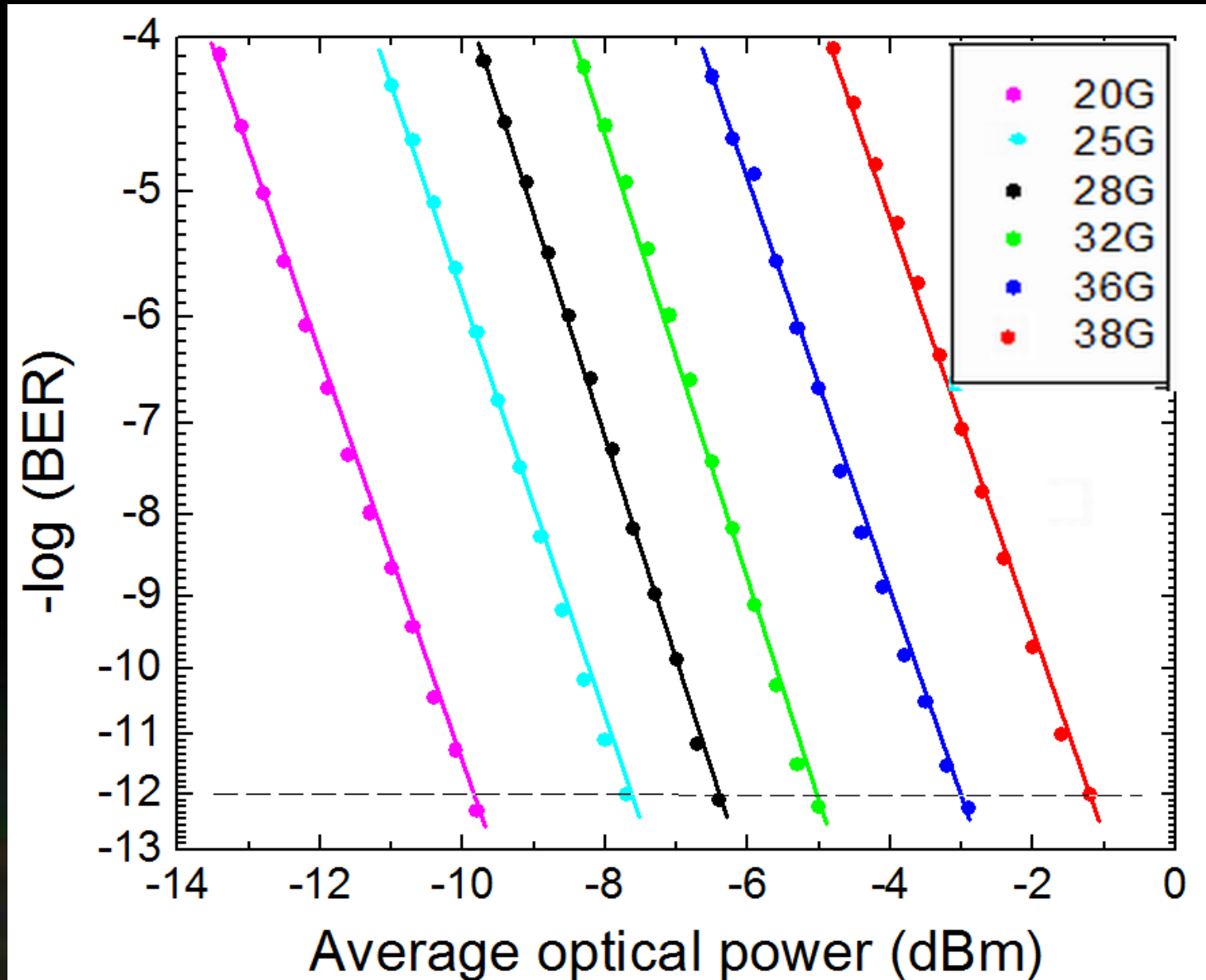
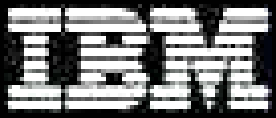


25Gbps performance

- ✓ Ge WG detector integrated with CMOS Circuitry
- ✓ 25Gbps stable operation
- ✓ Sensitivity -8.3dBm at 25Gbps

H.Pan et al, CLEO, May 2012 PDP session

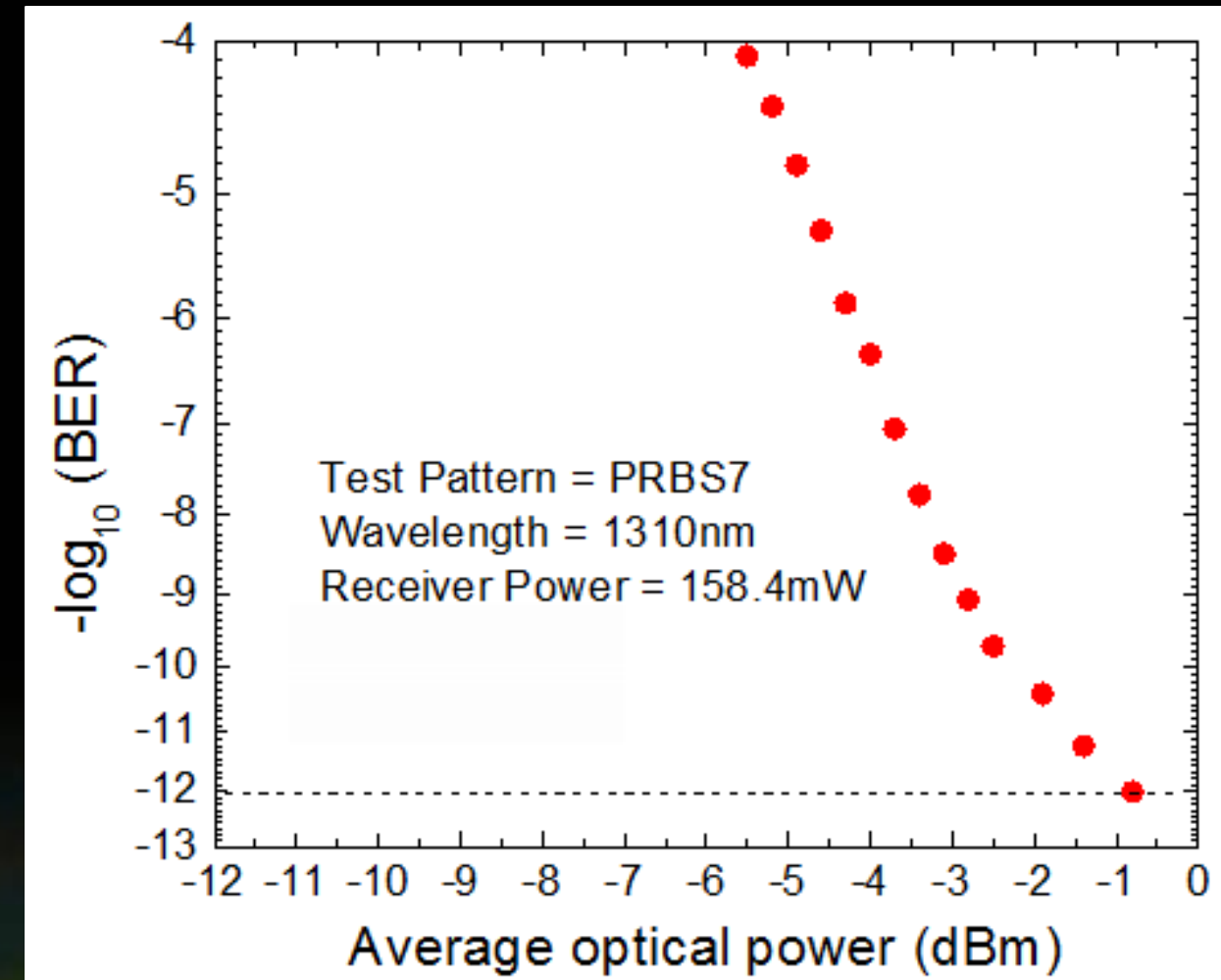
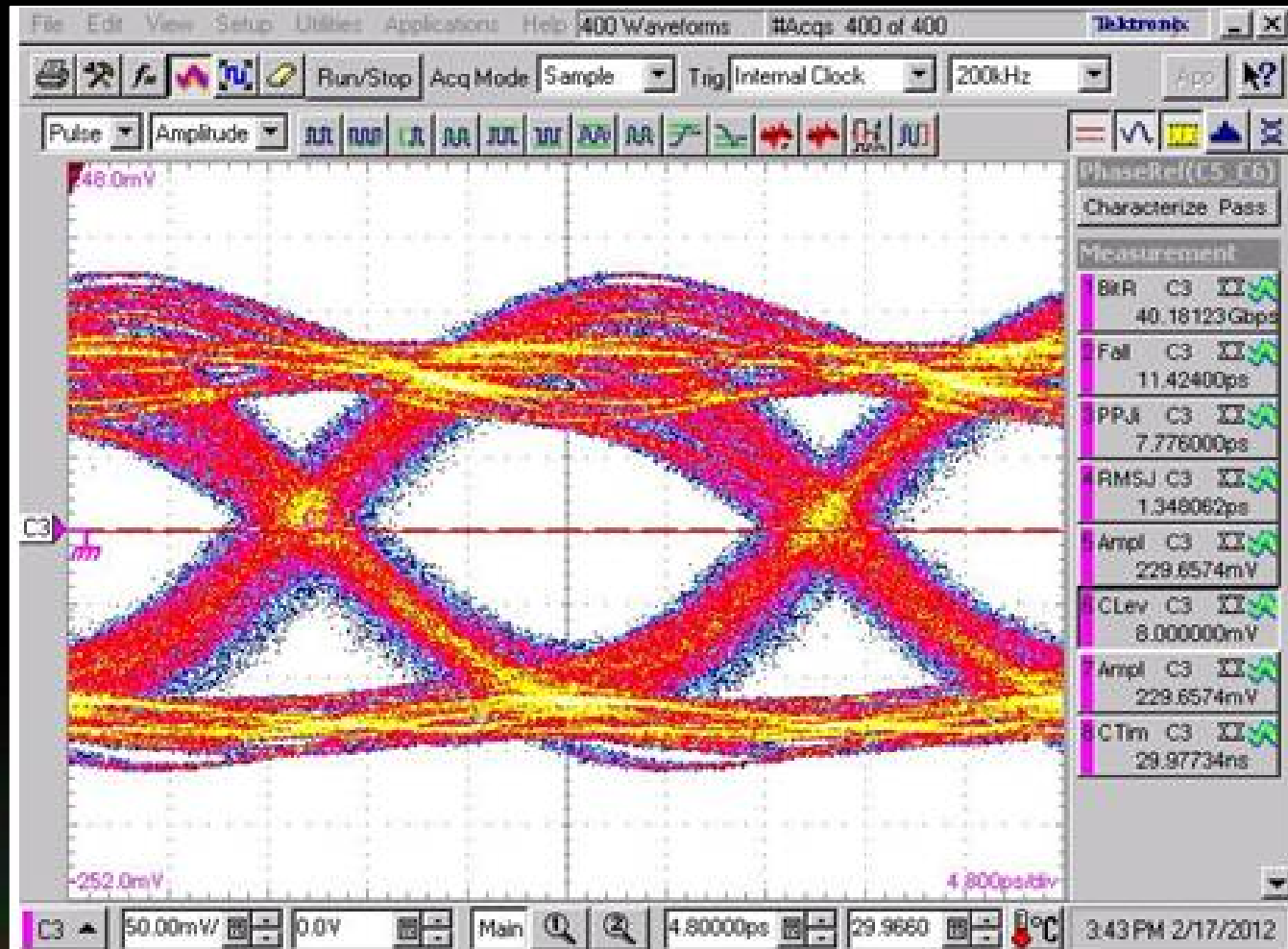
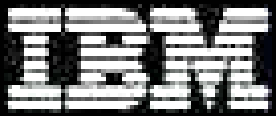
Performance beyond 25G



- ✓ Sensitivity -5.0 dBm at 32Gbps
- ✓ Power efficiency 1.5pJ/bit at 32Gbps

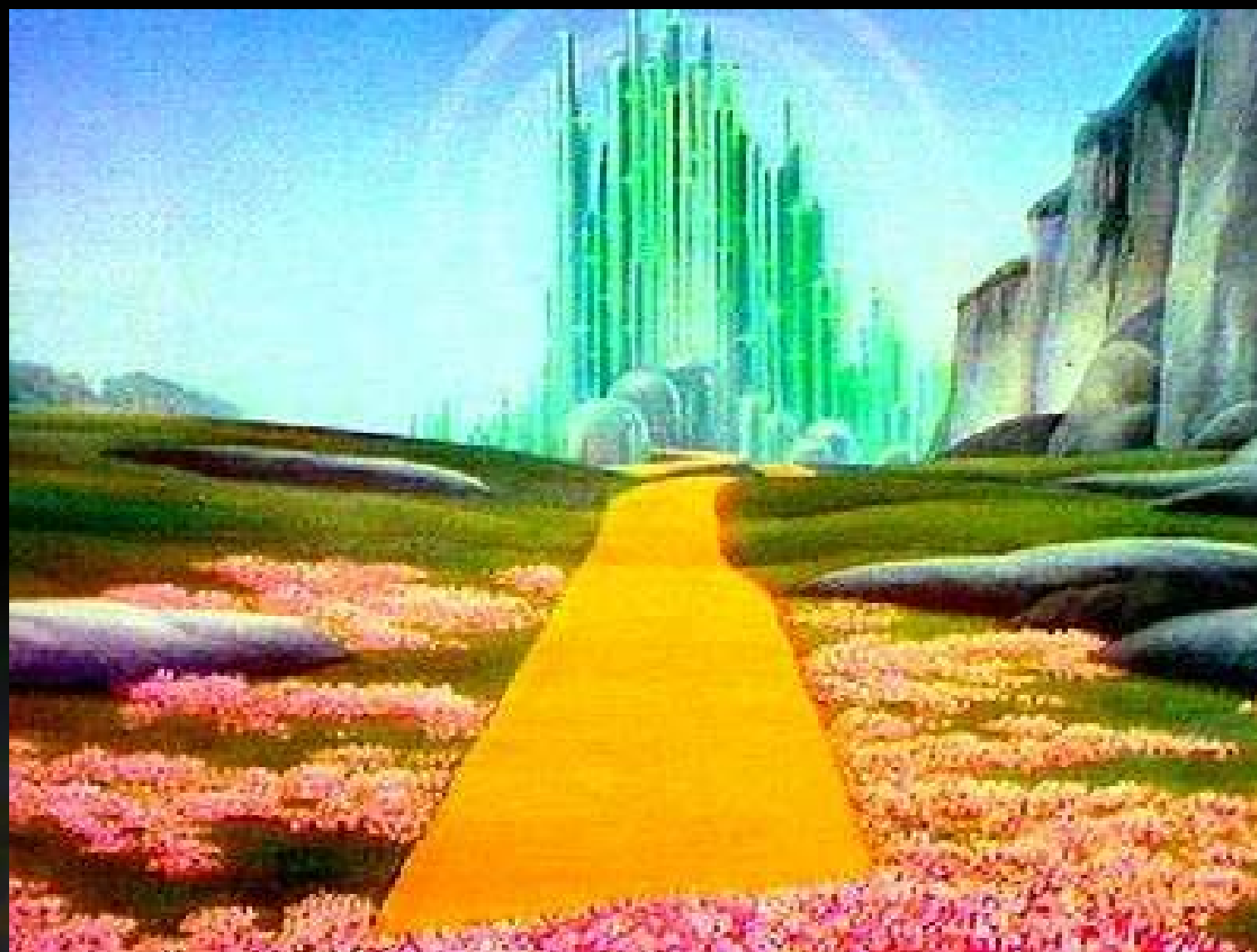
H.Pan et al, CLEO, May 2012 PDP session

Performance at 40G



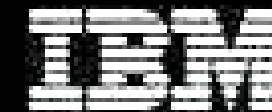
✓ Error-free ($\text{BER} < 1\text{e-}12$) up to 40Gbps

H.Pan et al, CLEO, May 2012 PDP session



Follow the YBR

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